









CC2652P JAJSI59C - OCTOBER 2019 - REVISED APRIL 2024

CC2652P パワー アンプを内蔵した SimpleLink™ マルチプロトコル 2.4GHz ワイヤレス MCU

1 特長

- マイコン
 - 強力な 48MHz Arm® Cortex®-M4F プロセッサ
 - EEMBC CoreMark® スコア:148
 - 352kB のインシステム プログラマブル フラッシュ
 - プロトコルおよびライブラリ機能用の 256kB ROM
 - 8kB のキャッシュ SRAM (汎用 RAM としても使用 可能)
 - 80kB の超低リーク SRAM。 SRAM は動作の信頼 性を高めるためパリティで保護。
 - 2ピン cJTAG および JTAG デバッグ
 - OTA (Over-the-air) 更新をサポート
- 4kB の SRAM を搭載した超低消費電力センサコント
 - センサ データのサンプリング、保存、処理
 - システム **CPU** から独立して動作
 - 高速ウェークアップによる低消費電力動作
- TI-RTOS、ドライバ、ブートローダ、Bluetooth® 5.2 Low Energy コントローラ、IEEE 802.15.4 MAC を ROM に配置してアプリケーション サイズを最適化
- RoHS 準拠のパッケージ
 - 7mm × 7mm ∅ RGZ VQFN48 (26 GPIO)
- ペリフェラル
 - デジタルペリフェラルを任意の GPIO に接続可能
 - 4×32 ビットまたは 8×16 ビットの汎用タイマ
 - 12 ビット ADC、200k サンプル / 秒、8 チャネル
 - 内部リファレンス DAC を搭載した 2 つのコンパレ

(連続時間 ×1、超低消費電力 ×1)

- プログラマブル電流ソース
- UART×2
- SSI ×2 (SPI、MICROWIRE、TI)
- I²C および I²S
- リアルタイム クロック (RTC)
- AES 128 および 256 ビット暗号化アクセラレータ
- ECC および RSA 公開鍵ハードウェア アクセラレ
- SHA2 アクセラレータ (SHA-512 までのフル スイ **一**ト)
- 真性乱数生成器 (TRNG)
- 静電容量式センシング、最大8チャネル
- 温度およびバッテリモニタを内蔵
- 外部システム
 - オンチップの降圧型 DC/DC コンバータ

低消費電力

- アクティブ モードの RX: 6.9mA
- アクティブ モードの TX (0dBm): 7.3mA
- アクティブ モードの TX (5dBm): 9.6mA
- アクティブ モードの TX (+10dBm): 22mA
- アクティブ モードの TX (+20dBm): 85mA
- アクティブ モードの MCU 48MHz (CoreMark): 3.4mA (71µA/MHz)
- センサコントローラ、低消費電力モード、2MHz、無 限ループ動作:30.1µA
- センサ コントローラ、アクティブ モード、24MHz、無 限ループ動作: 808µA
- スタンバイ:0.94µA (RTC オン、80kB RAM および CPU 保持)
- シャットダウン:150nA (外部イベントでウェークアッ プ)

無線部

- Bluetooth 5.2 Low Energy およびそれ以前の LE 仕様、IEEE 802.15.4 PHY および MAC と互換性 がある 2.4GHz RF トランシーバ
- 3線式、2線式、1線式 PTA の共存メカニズム
- 優れたレシーバ感度: 802.15.4 (2.4GHz) で -100dBm、 Bluetooth 125kbps (LE Coded PHY) で -105dBm
- 温度補償付きで最大 +20dBm の出力電力
- 国際的な無線周波数規制への準拠を目標としたシ ステムに最適
 - EN 300 328、(欧州)
 - EN 300 440 カテゴリ 2
 - FCC CFR47 Part 15
 - ARIB STD-T66 (日本)
- ワイヤレス プロトコル
 - Thread, Zigbee[®], Bluetooth[®] 5.2 Low Energy, IEEE 802.15.4、IPv6 対応スマート オブジェクト (6LoWPAN)、独自システム、SimpleLink™ TI 15.4 スタック (2.4GHz)、DMM (ダイナミック マルチプロ トコル マネージャ)ドライバ。
- 開発ツールとソフトウェア
 - SimpleLink™ LOWPOWER F2 ソフトウェア開発 キット (SDK)
 - SmartRF™ Studio による簡素な無線構成
 - Sensor Controller Studio により低消費電力のセ ンシング アプリケーションを構築



2 アプリケーション

- 2400MHz~2480MHz の ISM および SRD システム
 - (最小 4kHz の受信帯域幅
- ビルオートメーション
 - ビルディングのセキュリティシステム モーション検 出器、電子スマートロック、ドアおよび窓センサ、ガ レージドアシステム、ゲートウェイ
 - HVAC サーモスタット、ワイヤレス環境センサ、 HVAC システム コントローラ、ゲートウェイ
 - 防火システム 煙および熱感知器、火災警報制御パネル (FACP)
 - ビデオ監視 IP ネットワーク カメラ
 - エレベータとエスカレータ エレベータとエスカレータのエレベータメイン制御パネル
- グリッド インフラ
 - スマートメータ 水道メータ、ガスメータ、電気メータ、ヒートコストアロケータ
 - グリッド通信 無線通信 長距離センサ アプリケーション

- その他の代替エネルギー 環境発電
- 産業用輸送 アセットトラッキング
- ファクトリ オートメーション / 制御
- 医療用
- 電子 POS (EPOS) 電子棚札 (ESL)
- 通信機器
 - 有線ネットワーク 無線 LAN または Wi-Fi アクセス ポイント、エッジ ルータ、小規模企業向けルータ
- パーソナル エレクトロニクス
 - ポータブル電子機器 RF スマート遠隔制御
 - ホームシアターおよびエンターテインメント スマートスピーカ、スマートスマートディスプレイ、セットアップボックス
 - ネットワーク接続の周辺機器 民生用ワイヤレス モジュール、ポインティング デバイス、キーボードと キーパッド
 - ゲーム 電子玩具とロボット玩具
 - ウェアラブル (医療以外) スマートトラッカー、スマート衣料

3 概要

SimpleLink™ CC2652P デバイスはマルチプロトコルの 2.4GHz ワイヤレス マイコン (MCU) です。本デバイスは Thread、Zigbee®、Bluetooth® 5.2 Low Energy、IEEE 802.15.4、IPv6 対応スマート オブジェクト (6LoWPAN)、TI 15.4 スタック (2.4GHz) を含む独自システム、DMM (ダイナミック マルチプロトコル マネージャ) ドライバを使った同時マルチプロトコルをサポートしています。本デバイスは、ビル セキュリティシステム、HVAC、医療、有線ネットワーク、携帯型電子機器、ホーム シアター / エンターテインメント、ネットワーク接続周辺機器の市場の低消費電力の無線通信と先進センシングに最適化されています。このデバイスの主な特長を以下に示します。

- SimpleLink™ LOWPOWER F2 ソフトウェア開発キット (SDK) で幅広いプロトコル スタックを柔軟にサポート。
- クラス最小の送信時消費電流 (85mA) を特長とする内蔵の +20dBm ハイパワー アンプを使った長距離および低消費電力アプリケーションの実現
- ボタン型電池を使って 22mA の送信時消費電流、+10dBm の出力で動作
- 0.94μA の小さいスタンバイ電流 (全 RAM 保持) により、ワイヤレス アプリケーションのバッテリ駆動時間を延長
- 産業用温度に対応し、85℃で 5µA の最小スタンバイ電流
- 高速ウェークアップ機能を備えたプログラマブルな自律型超低消費電力センサコントローラ CPU による先進センシング。たとえば、このセンサコントローラは、1µA のシステム電流で 1Hz の ADC サンプリングが可能です。
- 潜在的な放射線イベントによるデータの破損を防止する常時オン SRAM パリティによる、産業用市場向けの中断のない長い動作寿命のための小さい SER (ソフトエラー レート) FIT (Failure-in-time、故障率)
- 柔軟性の高い低消費電力 RF トランシーバ機能を備えた専用のソフトウェア制御無線コントローラ (Arm® Cortex® -M0) により、複数の物理層および RF 規格をサポート
- Bluetooth® Low Energy (125kbps の LE Coded PHY で -105dBm) に対応する優れた無線感度および堅牢 (選択 度、ブロッキング) 性能。

CC2652P デバイスは SimpleLink™ MCU プラットフォームの一部です。このプラットフォームは Wi-Fi®、Bluetooth Low Energy、Thread、Zigbee、Sub-1GHz MCU、ホスト MCU で構成されます。CC2652P は、ピン互換のパッケージ オプションを備えた、32kB~704kB のフラッシュ サイズに対応するスケーラブルな製品ラインアップの一部であり、シングルコア ソフトウェア開発キット (SDK) と豊富なツール セットを備えた、共通の使いやすい開発環境を共有しています。SimpleLink™ プラットフォームを 1 回統合すれば、製品ラインアップのどのデバイスの組み合わせでも設計に追加できる

¹ See サポートしているプロトコル規格、変調フォーマット、データレートの詳細については、RF コアを参照してください。



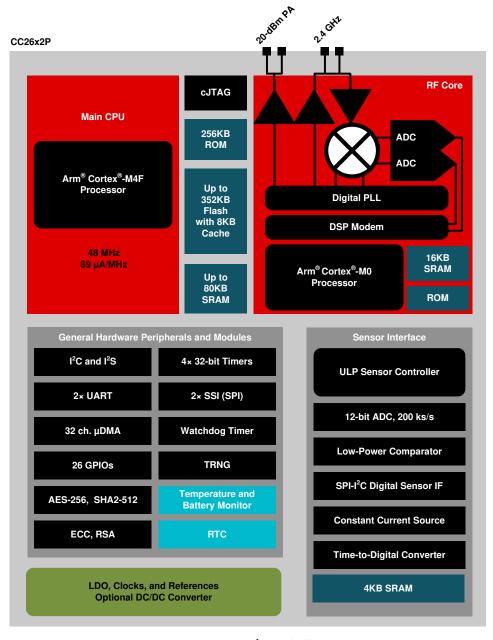
ので、設計要件変更の際もコードを高度に再利用できます。詳細については、SimpleLink™ MCU プラットフォームを参照してください。

製品情報

部品番 号 ⁽¹⁾	パッケージ	パッケージ サイズ
CC2652P1FRGZ	VQFN (48)	7.00mm × 7.00mm

(1) 詳細については、セクション 12 参照してください。

4機能ブロック図



CC2652P ブロック図



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Product Folder Links: CC2652P



5 Device Comparison

				F	RADIC	SUP	POR1	Г								PA	CKA	GE S	ΙΖΕ	
Device	Sub-1GHz Prop.	2.4GHz Prop.	Wireless M-Bus	mioty	Wi-SUN®	Sidewalk	Bluetooth® LE	Zigbee	Thread	Multiprotocol	+20dBm PA	FLASH (kB)	RAM + Cache (kB)	GPIO	4 × 4 mm VQFN (24)	4 × 4 mm VQFN (32)	5 × 5 mm VQFN (32)	5 × 5 mm VQFN (40)	7 × 7 mm VQFN (48)	8 × 8 mm VQFN (64)
CC1310	√		√	√								32-128	16-20 + 8	10-30		√	√		√	
CC1311R3	√		√	√								352	32 + 8	22-30				1	√	
CC1311P3	√		√	$\sqrt{}$							√	352	32 + 8	26					$\sqrt{}$	
CC1312R	√		√	1	√							352	80 + 8	30					√	
CC1312R7	1		√	V	√	√				√		704	144 + 8	30					√	
CC1314R10	√		√	√	√	√				√		1024	256 + 8	30-46					√	√
CC1352R	√	√	√	V	√		√	√	√	√		352	80 + 8	28					√	
CC1354R10	√	√	√	1	√		√	√	1	√		1024	256 + 8	28-42					√	√
CC1352P	√	√	√	1	√		1	√	1	√	√	352	80 + 8	26					√	
CC1352P7	√	√	√	1	√	√	1	√	1	√	√	704	144 + 8	26					√	
CC1354P10	√	√	√	1	√	√	√	√	1	√	√	1024	256 + 8	26-42					√	√
CC2340R5 ⁽¹⁾		√					√	√	1			512	36	12-26	1			1		
CC2640R2F							√					128	20 + 8	10-31		1	√		√	
CC2642R							1					352	80 + 8	31					√	
CC2642R-Q1							1					352	80 + 8	31					√	
CC2651R3		√					√	√				352	32 + 8	23-31				1	√	
CC2651P3		√					√	√			1	352	32 + 8	22-26				1	√	
CC2652R		√					√	√	1	√		352	80 + 8	31					√	
CC2652RB		√					1	√	1	√		352	80 + 8	31					√	
CC2652R7		√					1	√	1	√		704	144 + 8	31					√	
CC2652P		√					1	√	√	√	1	352	80 + 8	26					√	
CC2652P7		√					√	√	√	√	√	704	144 + 8	26					√	
CC2674R10		√					√	√	√	√		1024	256 + 8	31-45					√	√
CC2674P10		√					√	√	√	√	1	1024	256 + 8	26-45					√	√
CC2653P10		√					√	√	√	√	V	1024	128 + 8	26					√	

⁽¹⁾ Zigbee and Thread support enabled by future software update

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Product Folder Links: CC2652P



6 Pin Configuration and Functions

6.1 Pin Diagram—RGZ Package (Top View)

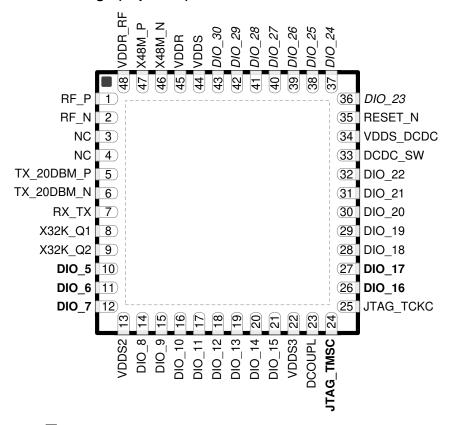


図 6-1. RGZ (7mm × 7mm) Pinout, 0.5mm Pitch (Top View)

The following I/O pins marked in 図 6-1 in **bold** have high-drive capabilities:

- Pin 10, DIO_5
- Pin 11, DIO_6
- Pin 12, DIO_7
- Pin 24, JTAG_TMSC
- Pin 26, DIO_16
- Pin 27, DIO 17

The following I/O pins marked in **図 6-1** in *italics* have analog capabilities:

- Pin 36, DIO 23
- Pin 37, DIO 24
- Pin 38, DIO 25
- Pin 39, DIO 26
- Pin 40, DIO 27
- Pin 41, DIO_28
- Pin 42, DIO_29
- Pin 43, DIO_30



6.2 Signal Descriptions—RGZ Package

表 6-1. Signal Descriptions—RGZ Package

PIN		I/O	TYPE	DESCRIPTION
NAME	NO.	1/0	ITPE	DESCRIPTION
DCDC_SW	33	_	Power	Output from internal DC/DC converter ⁽¹⁾
DCOUPL	23	_	Power	For decoupling of internal 1.27V regulated digital-supply ⁽²⁾
DIO_5	10	I/O	Digital	GPIO, high-drive capability
DIO_6	11	I/O	Digital	GPIO, high-drive capability
DIO_7	12	I/O	Digital	GPIO, high-drive capability
DIO_8	14	I/O	Digital	GPIO
DIO_9	15	I/O	Digital	GPIO
DIO_10	16	I/O	Digital	GPIO
DIO_11	17	I/O	Digital	GPIO
DIO_12	18	I/O	Digital	GPIO
DIO_13	19	I/O	Digital	GPIO
DIO_14	20	I/O	Digital	GPIO
DIO_15	21	I/O	Digital	GPIO
DIO_16	26	I/O	Digital	GPIO, JTAG_TDO, high-drive capability
DIO_17	27	I/O	Digital	GPIO, JTAG_TDI, high-drive capability
DIO_18	28	I/O	Digital	GPIO
DIO_19	29	I/O	Digital	GPIO
DIO_20	30	I/O	Digital	GPIO
DIO_21	31	I/O	Digital	GPIO
DIO_22	32	I/O	Digital	GPIO
DIO_23	36	I/O	Digital or Analog	GPIO, analog capability
DIO_24	37	I/O	Digital or Analog	GPIO, analog capability
DIO_25	38	I/O	Digital or Analog	GPIO, analog capability
DIO_26	39	I/O	Digital or Analog	GPIO, analog capability
DIO_27	40	I/O	Digital or Analog	GPIO, analog capability
DIO_28	41	I/O	Digital or Analog	GPIO, analog capability
DIO_29	42	I/O	Digital or Analog	GPIO, analog capability
DIO_30	43	I/O	Digital or Analog	GPIO, analog capability
EGP		_	GND	Ground – exposed ground pad ⁽³⁾
JTAG_TMSC	24	I/O	Digital	JTAG TMSC, high-drive capability
JTAG_TCKC	25	I	Digital	JTAG TCKC
RESET_N	35	I	Digital	Reset, active low. No internal pullup resistor
RF_P	1	_	RF	Positive RF input signal to LNA during RX Positive RF output signal from PA during TX
RF_N	2	_	RF	Negative RF input signal to LNA during RX Negative RF output signal from PA during TX
RX_TX	7	_	RF	Optional bias pin for the RF LNA
TX_20DBM_P	5	_	RF	Positive high-power TX signal
TX_20DBM_N	6	_	RF	Negative high-power TX signal
VDDR	45	_	Power	Internal supply, must be powered from the internal DC/DC converter or the internal LDO ⁽²⁾ (4) (6)
VDDR_RF	48	_	Power	Internal supply, must be powered from the internal DC/DC converter or the internal LDO ⁽²⁾ (5) (6)



表 6-1. Signal Descriptions—RGZ Package (続き)

PIN		I/O	TYPE	DESCRIPTION	
NAME	NO.	"0	IIFE	PE DESCRIPTION	
VDDS	44	_	Power	1.8V to 3.8V main chip supply ⁽¹⁾	
VDDS2	13	_	Power	1.8V to 3.8V DIO supply ⁽¹⁾	
VDDS3	22	_	Power	1.8V to 3.8V DIO supply ⁽¹⁾	
VDDS_DCDC	34	_	Power	1.8V to 3.8V DC/DC converter supply	
X48M_N	46	_	Analog	48MHz crystal oscillator pin 1	
X48M_P	47	_	Analog	48MHz crystal oscillator pin 2	
X32K_Q1	8	_	Analog	32kHz crystal oscillator pin 1	
X32K_Q2	9	_	Analog	32kHz crystal oscillator pin 2	

- (1) For more details, see technical reference manual listed in セクション 10.2.
- (2) Do not supply external circuitry from this pin.
- (3) EGP is the only ground connection for the device. Good electrical connection to device ground on printed circuit board (PCB) is imperative for proper device operation.
- (4) If internal DC/DC converter is not used, this pin is supplied internally from the main LDO.
- (5) If internal DC/DC converter is not used, this pin must be connected to VDDR for supply from the main LDO.
- (6) Output from internal DC/DC and LDO is trimmed to 1.68V.

6.3 Connections for Unused Pins and Modules

表 6-2. Connections for Unused Pins

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FUNCTION	SIGNAL NAME	PIN NUMBER	ACCEPTABLE PRACTICE(1)	PREFERRED PRACTICE ⁽¹⁾					
GPIO	DIO_n	10–12 14–21 26–32 36–43	NC or GND	NC					
32.768kHz crystal	X32K_Q1	8	NC or GND	NC					
32.7 OOKI IZ CI YSIAI	X32K_Q2	9	INC OF GIND	NO					
No Connects	NC	3–4	NC	NC					
DC/DC converter ⁽²⁾	DCDC_SW	33	NC	NC					
DC/DC converter	VDDS_DCDC	34	VDDS	VDDS					

- (1) NC = No connect
- When the DC/DC converter is not used, the inductor between DCDC_SW and VDDR can be removed. VDDR and VDDR_RF must still be connected and the 22µF DCDC capacitor must be kept on the VDDR net.

Product Folder Links: CC2652P

資料に関するフィードバック(ご意見やお問い合わせ) を送信

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1) (2)

			MIN	MAX	UNIT
VDDS ⁽³⁾	Supply voltage		-0.3	4.1	V
	Voltage on any digital pir	age on any digital pin ^{(4) (5)} age on crystal oscillator pins, X32K_Q1, X32K_Q2, X48M_N and X48M_P		VDDS + 0.3, max 4.1	V
	Voltage on crystal oscilla	tor pins, X32K_Q1, X32K_Q2, X48M_N and X48M_P	-0.3	VDDR + 0.3, max 2.25	V
		Voltage scaling enabled	-0.3	VDDS	
V _{in}	Voltage on ADC input	Voltage scaling disabled, internal reference	-0.3	1.49	V
		Voltage scaling disabled, VDDS as reference	-0.3	VDDS / 2.9	
	Input level, RF pins			5	dBm
T _{stg}	Storage temperature		-40	150	°C

- (1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime
- All voltage values are with respect to ground, unless otherwise noted.
- (3) VDDS DCDC, VDDS2 and VDDS3 must be at the same potential as VDDS.
- Including analog capable DIOs.
- (5) Injection current is not supported on any GPIO pin

7.2 ESD Ratings

				VALUE	UNIT
V	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS001 ⁽¹⁾	All pins	±2000	V
V _{ESD}	Liectiostatic discharge	Charged device model (CDM), per JESD22-C101 ⁽²⁾	All pins	±500	V

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
- JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
Operating junction temperature	-40	105	°C
Operating supply voltage (VDDS)	1.8	3.8	V
Rising supply voltage slew rate	0	100	mV/μs
Falling supply voltage slew rate ⁽¹⁾	0	20	mV/μs

⁽¹⁾ For small coin-cell batteries, with high worst-case end-of-life equivalent source resistance, a 22µF VDDS input capacitor must be used to ensure compliance with this slew rate.

7.4 Power Supply and Modules

over operating free-air temperature range (unless otherwise noted)

PARAMETER		MIN TYP MAX	UNIT
VDDS Power-on-Reset (POR) threshold		1.1 - 1.55	V
VDDS Brown-out Detector (BOD) (1)	Rising threshold	1.77	V
VDDS Brown-out Detector (BOD), before initial boot (2)	Rising threshold	1.70	V
VDDS Brown-out Detector (BOD) (1)	Falling threshold	1.75	V

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- For boost mode (VDDR =1.95V), TI drivers software initialization will trim VDDS BOD limits to maximum (approximately 2.0V)
- Brown-out Detector is trimmed at initial boot, value is kept until device is reset by a POR reset or the RESET_N pin

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7.5 Power Consumption—Power Modes

When measured on the CC1352PEM-XD7793-XD24-PA24 reference design with T_c = 25°C, V_{DDS} = 3.0V with DC/DC enabled unless otherwise noted.

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Core Curr	ent Consumption				
	Reset and Shutdown	Reset. RESET_N pin asserted or VDDS below power-on-reset threshold	150		nA
	Shuldown	Shutdown. No clocks running, no retention	150		
	Standby without cache	RTC running, CPU, 80kB RAM and (partial) register retention. RCOSC_LF	0.94		μA
	retention	RTC running, CPU, 80kB RAM and (partial) register retention XOSC_LF	1.09		μΑ
core	Standby RCOSC_LF	RTC running, CPU, 80kB RAM and (partial) register retention. RCOSC_LF	3.2		μΑ
	with cache retention	RTC running, CPU, 80kB RAM and (partial) register retention. XOSC_LF	3.3		μΑ
	Idle	Supply Systems and RAM powered RCOSC_HF	675		μΑ
	Active	MCU running CoreMark at 48MHz RCOSC_HF	3.39		mA
Periphera	I Current Consumption ⁽¹⁾ ,	(2)			
	Peripheral power domain	Delta current with domain enabled	97.7		
	Serial power domain	Delta current with domain enabled	7.2		
	RF Core	Delta current with power domain enabled, clock enabled, RF core idle	210.9		
	μDMA	Delta current with clock enabled, module is idle	63.9		
	Timers	Delta current with clock enabled, module is idle ⁽⁵⁾	81.0		
I _{peri}	I2C	Delta current with clock enabled, module is idle	10.1		μA
	I2S	Delta current with clock enabled, module is idle	26.3		
	SSI	Delta current with clock enabled, module is idle	82.9		
	UART	Delta current with clock enabled, module is idle ⁽³⁾	167.5		
	CRYPTO (AES)	Delta current with clock enabled, module is idle ⁽⁴⁾	25.6		
	PKA	Delta current with clock enabled, module is idle	84.7		
	TRNG	Delta current with clock enabled, module is idle	35.6		
Sensor Co	ontroller Engine Consump	tion			
	Active mode	24MHz, infinite loop	808.5		^
ISCE	Low-power mode	2MHz, infinite loop	30.1		μA

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7.6 Power Consumption—Radio Modes

When measured on the CC1352PEM-XD7793-XD24-PA24 reference design with T_c = 25°C, V_{DDS} = 3.0V with DC/DC enabled unless otherwise noted.

High-power PA connected to V_{DDS} unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Radio receive current	2440MHz		6.9		mA
Radio transmit current 2.4 GHz PA	0dBm output power setting 2440MHz		7.0		mA
(BLE)	+5dBm output power setting 2440MHz		9.2		mA
Radio transmit current High-power PA	+20dBm output power setting 2440MHz. VDDS = 3.3V		85		mA
Radio transmit current High-power PA, 10dBm configuration ⁽¹⁾	+10dBm output power setting 2440MHz VDDR = 1.67V		22		mA

(1) Measured on evaluation board (See Optimizing the CC1352P and CC2652P for Coin Cell Operation at 10dBm Output Power.)

7.7 Nonvolatile (Flash) Memory Characteristics

Over operating free-air temperature range and $V_{DDS} = 3.0V$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Flash sector size			8		KB
Supported flash erase cycles before failure, full bank ^{(1) (5)}		30			k Cycles
Supported flash erase cycles before failure, single sector ⁽²⁾		60			k Cycles
Maximum number of write operations per row before sector erase ⁽³⁾				83	Write Operations
Flash retention	85°C	11.4			Years at 85°C
Flash sector erase current	Average delta current		10.7		mA
Flash sector erase time ⁽⁴⁾	Zero cycles		10		ms
Flash write current	Average delta current, 4 bytes at a time		6.2		mA
Flash write time ⁽⁴⁾	4 bytes at a time		21.6		μs

- (1) A full bank erase is counted as a single erase cycle on each sector
- (2) Up to four customer-designated sectors can be individually erased an additional 30k times beyond the baseline bank limitation of 30k cycles
- (3) Each wordline is 2048 bits (or 256 bytes) wide. This limitation corresponds to sequential memory writes of 4 (3.1) bytes minimum per write over a whole wordline. If additional writes to the same wordline are required, a sector erase is required once the maximum number of write operations per row is reached.
- (4) This number is dependent on Flash aging and increases over time and erase cycles
- (5) Aborting flash during erase or program modes is not a safe operation.

7.8 Thermal Resistance Characteristics

		PACKAGE	
	THERMAL METRIC(1)	RGZ (VQFN)	UNIT
		48 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	23.4	°C/W ⁽²⁾
R ₀ JC(top)	Junction-to-case (top) thermal resistance	13.3	°C/W ⁽²⁾
R _{θJB}	Junction-to-board thermal resistance	8.0	°C/W ⁽²⁾
Ψлт	Junction-to-top characterization parameter	0.1	°C/W ⁽²⁾
ΨЈВ	Junction-to-board characterization parameter	7.9	°C/W ⁽²⁾
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	1.7	°C/W ⁽²⁾

(1) For more information about traditional and new thermal metrics, see Semiconductor and IC Package Thermal Metrics.

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(2) °C/W = degrees Celsius per watt.

7.9 RF Frequency Bands

Over operating free-air temperature range (unless otherwise noted).

PARAMETER	MIN	TYP MAX	UNIT
Frequency bands	2360	2500	MHz

7.10 Bluetooth Low Energy—Receive (RX)

Measured on the CC1352PEM-XD7793-XD24-PA24 reference design with T_c = 25°C, V_{DDS} = 3.0V, f_{RF} = 2440MHz with DC/DC enabled and the high-power PA connected to V_{DDS} unless otherwise noted.

All measurements are performed at the antenna input with a combined RX and TX path, except for the high-power PA, which is measured at a dedicated antenna connection. All measurements are performed and conducted.

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
125kbps (LE Coded)			'	
Receiver sensitivity	Differential mode. BER = 10 ⁻³	-105		dBm
Receiver saturation	Differential mode. BER = 10 ⁻³	>5		dBm
Frequency error tolerance	Difference between the incoming carrier frequency and the internally generated carrier frequency	> (-300 / 300)		kHz
Data rate error tolerance	Difference between the incoming data rate and the internally generated data rate (37-byte packets)	> (-320 / 240)		ppm
Data rate error tolerance	Difference between the incoming data rate and the internally generated data rate (255-byte packets)	> (-125 / 125)		ppm
Co-channel rejection ⁽¹⁾	Wanted signal at –79dBm, modulated interferer in channel, BER = 10 ⁻³	-1.5		dB
Selectivity, ±1MHz ⁽¹⁾	Wanted signal at –79dBm, modulated interferer at ±1MHz, BER = 10 ⁻³	8 / 4.5(2)		dB
Selectivity, ±2MHz ⁽¹⁾	Wanted signal at –79dBm, modulated interferer at ±2MHz, BER = 10 ⁻³	44 / 39 (2)		dB
Selectivity, ±3MHz ⁽¹⁾	Wanted signal at –79dBm, modulated interferer at ±3MHz, BER = 10 ⁻³	46 / 44 ⁽²⁾		dB
Selectivity, ±4MHz ⁽¹⁾	Wanted signal at –79dBm, modulated interferer at ±4MHz, BER = 10 ⁻³	44 / 46 ⁽²⁾		dB
Selectivity, ±6MHz ⁽¹⁾	Wanted signal at –79dBm, modulated interferer at ≥ ±6MHz, BER = 10 ⁻³	48 / 44 ⁽²⁾		dB
Selectivity, ±7MHz	Wanted signal at −79dBm, modulated interferer at ≥ ±7MHz, BER = 10 ⁻³	51 / 45 ⁽²⁾		dB
Selectivity, Image frequency ⁽¹⁾	Wanted signal at –79dBm, modulated interferer at image frequency, BER = 10 ⁻³			dB
Selectivity, Image frequency ±1MHz ⁽¹⁾	Note that Image frequency + 1MHz is the co-channel – 1MHz. Wanted signal at –79dBm, modulated interferer at ±1MHz from image frequency, BER = 10 ⁻³	4.5 / 44 (2)		dB
500kbps (LE Coded)				
Receiver sensitivity	Differential mode. BER = 10 ⁻³	-100		dBm
Receiver saturation	Differential mode. BER = 10 ⁻³	> 5		dBm
Frequency error tolerance	Difference between the incoming carrier frequency and the internally generated carrier frequency	> (-300 / 300)		kHz
Data rate error tolerance	Difference between the incoming data rate and the internally generated data rate (37-byte packets)	> (-450 / 450)		ppm
Data rate error tolerance	Difference between the incoming data rate and the internally generated data rate (255-byte packets)	> (–175 / 175)		ppm
Co-channel rejection ⁽¹⁾	Wanted signal at –72dBm, modulated interferer in channel, BER = 10 ⁻³	-3.5		dB
Selectivity, ±1MHz ⁽¹⁾	Wanted signal at –72dBm, modulated interferer at ±1MHz, BER = 10 ⁻³	8 / 4 ⁽²⁾		dB
Selectivity, ±2MHz ⁽¹⁾	Wanted signal at –72dBm, modulated interferer at ±2MHz, BER = 10 ⁻³	44 / 37 (2)		dB

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7.10 Bluetooth Low Energy—Receive (RX) (続き)

Measured on the CC1352PEM-XD7793-XD24-PA24 reference design with T_c = 25°C, V_{DDS} = 3.0V, f_{RF} = 2440MHz with DC/DC enabled and the high-power PA connected to V_{DDS} unless otherwise noted.

All measurements are performed at the antenna input with a combined RX and TX path, except for the high-power PA, which is measured at a dedicated antenna connection. All measurements are performed and conducted.

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Selectivity, ±3MHz ⁽¹⁾	Wanted signal at –72dBm, modulated interferer at ±3MHz, BER = 10 ⁻³	46 / 46 ⁽²⁾		dB
Selectivity, ±4MHz ⁽¹⁾	Wanted signal at –72dBm, modulated interferer at ±4MHz, BER = 10 ⁻³	45 / 47 ⁽²⁾		dB
Selectivity, ±6MHz ⁽¹⁾	Wanted signal at –72dBm, modulated interferer at ≥ ±6MHz, BER = 10 ⁻³	46 / 45 ⁽²⁾		dB
Selectivity, ±7MHz	Wanted signal at –72dBm, modulated interferer at ≥ ±7MHz, BER = 10 ⁻³	49 / 45 ⁽²⁾		dB
Selectivity, Image frequency ⁽¹⁾	Wanted signal at –72dBm, modulated interferer at image frequency, BER = 10 ⁻³			dB
Selectivity, Image frequency ±1MHz ⁽¹⁾	Note that Image frequency + 1MHz is the co-channel – 1MHz. Wanted signal at –72dBm, modulated interferer at ±1MHz from image frequency, BER = 10 ⁻³	4 / 46 ⁽²⁾		dB
1Mbps (LE 1M)				
Receiver sensitivity	Differential mode. BER = 10 ⁻³	-97		dBm
Receiver saturation	Differential mode. BER = 10 ⁻³	> 5		dBm
Frequency error tolerance	Difference between the incoming carrier frequency and the internally generated carrier frequency	> (-350 / 350)		kHz
Data rate error tolerance	Difference between the incoming data rate and the internally generated data rate (37-byte packets)	> (-750 / 750)		ppm
Co-channel rejection ⁽¹⁾	Wanted signal at –67dBm, modulated interferer in channel, BER = 10 ⁻³	-6		dB
Selectivity, ±1MHz ⁽¹⁾	Wanted signal at –67dBm, modulated interferer at ±1MHz, BER = 10 ⁻³	7 / 4 ⁽²⁾		dB
Selectivity, ±2MHz ⁽¹⁾	Wanted signal at –67dBm, modulated interferer at ±2MHz, BER = 10 ⁻³	40 / 33 ⁽²⁾		dB
Selectivity, ±3MHz ⁽¹⁾	Wanted signal at –67dBm, modulated interferer at ±3MHz, BER = 10 ⁻³	36 / 41 ⁽²⁾		dB
Selectivity, ±4MHz ⁽¹⁾	Wanted signal at –67dBm, modulated interferer at ±4MHz, BER = 10 ⁻³	36 / 45 ⁽²⁾		dB
Selectivity, ±5MHz or more ⁽¹⁾	Wanted signal at –67dBm, modulated interferer at ≥ ±5MHz, BER = 10 ⁻³	40		dB
Selectivity, image frequency ⁽¹⁾	Wanted signal at –67dBm, modulated interferer at image frequency, BER = 10 ⁻³	33		dB
Selectivity, image frequency ±1MHz ⁽¹⁾	Note that Image frequency + 1MHz is the co-channel – 1MHz. Wanted signal at –67dBm, modulated interferer at ±1MHz from image frequency, BER = 10 ⁻³	4 / 41(2)		dB
Out-of-band blocking ⁽³⁾	30MHz to 2000MHz	-10		dBm
Out-of-band blocking	2003MHz to 2399MHz	-18		dBm
Out-of-band blocking	2484MHz to 2997MHz	-12		dBm
Out-of-band blocking	3000MHz to 12.75GHz	-2		dBm
Intermodulation	Wanted signal at 2402MHz, -64 dBm. Two interferers at 2405MHz and 2408MHz, respectively, at the given power level	-42		dBm
Spurious emissions, 30MHz to 1000MHz ⁽⁴⁾	Measurement in a 50Ω single-ended load	< -59		dBm
Spurious emissions, 1 to 12.75GHz ⁽⁴⁾	Measurement in a 50Ω single-ended load	< -47		dBm
RSSI dynamic range		70		dB
RSSI accuracy		±4		dB
2Mbps (LE 2M)				

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7.10 Bluetooth Low Energy—Receive (RX) (続き)

Measured on the CC1352PEM-XD7793-XD24-PA24 reference design with T_c = 25°C, V_{DDS} = 3.0V, f_{RF} = 2440MHz with DC/DC enabled and the high-power PA connected to V_{DDS} unless otherwise noted.

All measurements are performed at the antenna input with a combined RX and TX path, except for the high-power PA, which is measured at a dedicated antenna connection. All measurements are performed and conducted.

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Receiver sensitivity	Differential mode. Measured at SMA connector, BER = 10^{-3}	-92		dBm
Receiver saturation	Differential mode. Measured at SMA connector, BER = 10^{-3}	> 5		dBm
Frequency error tolerance	Difference between the incoming carrier frequency and the internally generated carrier frequency	> (-500 / 500)		kHz
Data rate error tolerance	Difference between the incoming data rate and the internally generated data rate (37-byte packets)	> (-700 / 750)		ppm
Co-channel rejection ⁽¹⁾	Wanted signal at –67dBm, modulated interferer in channel, BER = 10 ⁻³	-7		dB
Selectivity, ±2MHz ⁽¹⁾	Wanted signal at –67dBm, modulated interferer at ±2MHz, Image frequency is at –2MHz, BER = 10 ⁻³	8 / 4 ⁽²⁾		dB
Selectivity, ±4MHz ⁽¹⁾	Wanted signal at –67dBm, modulated interferer at ±4MHz, BER = 10 ⁻³	36 / 36 ⁽²⁾		dB
Selectivity, ±6MHz ⁽¹⁾	Wanted signal at –67dBm, modulated interferer at ±6MHz, BER = 10 ⁻³	37 / 36 ⁽²⁾		dB
Selectivity, image frequency ⁽¹⁾	Wanted signal at –67dBm, modulated interferer at image frequency, BER = 10 ⁻³	4		dB
Selectivity, image frequency ±2MHz ⁽¹⁾	Note that Image frequency + 2MHz is the Co-channel. Wanted signal at –67dBm, modulated interferer at ±2MHz from image frequency, BER = 10 ⁻³	-7 / 36 ⁽²⁾		dB
Out-of-band blocking ⁽³⁾	30MHz to 2000MHz	-16		dBm
Out-of-band blocking	2003MHz to 2399MHz	-21		dBm
Out-of-band blocking	2484MHz to 2997MHz	-15		dBm
Out-of-band blocking	3000MHz to 12.75 GHz	-12		dBm
Intermodulation	Wanted signal at 2402MHz, –64 dBm. Two interferers at 2408 and 2414MHz respectively, at the given power level	-38		dBm

- (1) Numbers given as I/C dB
- (2) X / Y, where X is +N MHz and Y is -N MHz
- (3) Excluding one exception at F_{wanted} / 2, per Bluetooth Specification
- (4) Suitable for systems targeting compliance with worldwide radio-frequency regulations ETSI EN 300 328 and EN 300 440 Class 2 (Europe), FCC CFR47 Part 15 (US), and ARIB STD-T66 (Japan)

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7.11 Bluetooth Low Energy—Transmit (TX)

Measured on the CC1352PEM-XD7793-XD24-PA24 reference design with T_c = 25°C, V_{DDS} = 3.0V, f_{RF} = 2440MHz with DC/DC enabled and high power PA connected to V_{DDS} unless otherwise noted.

All measurements are performed at the antenna input with a combined RX and TX path, except for high power PA which is measured at a dedicated antenna connection. All measurements are performed conducted.

PARAMETER		TEST CONDITIONS	MIN TYP	MAX	UNIT
General Parameters					
Max output power, high power PA	Differential mode, delivered to a sing	lle-ended 50 Ω load through a balun	19.5		dBm
Output power programmable range high power PA	Differential mode, delivered to a sing	lle-ended 50 Ω load through a balun	6		dB
Max output power, high power PA, 10dBm configuration ⁽⁴⁾	Differential mode, delivered to a sing	erential mode, delivered to a single-ended 50 Ω load through a balun			dBm
Output power programmable range high power PA, 10dBm configuration ⁽⁴⁾	Differential mode, delivered to a sing	ferential mode, delivered to a single-ended 50 Ω load through a balun			dB
Max output power, regular PA	Differential mode, delivered to a sing	le-ended 50 Ω load through a balun	5		dBm
Output power programmable range, regular PA	Differential mode, delivered to a sing	26		dB	
Spurious emissions ar	nd harmonics				
Spurious emissions, high-power PA ⁽¹⁾ (2)	f < 1GHz, outside restricted bands	_	< -36		dBm
	f < 1GHz, restricted bands FCC		< -55		dBm
	f > 1GHz, including harmonics	+20dBm setting	-37		dBm
Harmonics,	Second harmonic		-35		dBm
high-power PA ⁽¹⁾ (3)	Third harmonic		-42		dBm
	f < 1GHz, outside restricted bands		< -36		dBm
Spurious emissions,	f < 1GHz, restricted bands ETSI		< -54		dBm
high-power PA, 10dBm configuration ⁽¹⁾ (2) (4)	f < 1GHz, restricted bands FCC		< -55		dBm
	f > 1GHz, including harmonics	+10dBm setting ⁽⁴⁾	-41		dBm
Harmonics,	Second harmonic		< -42		dBm
high-power PA, 10dBm configuration ⁽¹⁾ (4)	Third harmonic		< -42		dBm
	f < 1GHz, outside restricted bands		< -36		dBm
Spurious emissions,	f < 1GHz, restricted bands ETSI		< -54		dBm
regular PA ⁽¹⁾	f < 1GHz, restricted bands FCC	, s.d.D.,	< -55		dBm
	f > 1GHz, including harmonics	- +5dBm setting	< -42		dBm
Harmonics,	Second harmonic	1	< -42		dBm
regular PA (1)	Third harmonic	1	< -42		dBm

- (1) Suitable for systems targeting compliance with worldwide radio-frequency regulations ETSI EN 300 328 and EN 300 440 Class 2 (Europe), FCC CFR47 Part 15 (US), and ARIB STD-T66 (Japan).
- (2) To ensure margins for passing FCC band edge requirements at 2483.5MHz, a lower than maximum output-power setting or less than 100% duty cycle may be used when operating at the upper BLE channel(s).
- (3) To ensure margins for passing FCC requirements for harmonic emission, duty cycling may be required. The CC1352P-2 LaunchPad reference design should also be reviewed as the filter provides higher attenuation of harmonics compared to the CC1352PEM-XD7793-XD24-PA24 reference design.
- (4) Measured on evaluation board as described in Optimizing the CC1352P and CC2652P for Coin Cell Operation at 10dBm Output Power.



7.12 Zigbee and Thread—IEEE 802.15.4-2006 2.4GHz (OQPSK DSSS1:8, 250kbps): RX

Measured on the CC1352PEM-XD7793-XD24-PA24 reference design with T_c = 25°C, V_{DDS} = 3.0V, f_{RF} = 2440MHz with DC/DC enabled and high power PA connected to V_{DDS} unless otherwise noted.

All measurements are performed at the antenna input with a combined RX and TX path, except for high power PA which is measured at a dedicated antenna connection. All measurements are performed conducted.

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
General Parameters			'	
Receiver sensitivity	PER = 1%	-100		dBm
Receiver saturation	PER = 1%	> 5		dBm
Adjacent channel rejection	Wanted signal at –82dBm, modulated interferer at ±5MHz, PER = 1%	36		dB
Alternate channel rejection	Wanted signal at –82dBm, modulated interferer at ±10MHz, PER = 1%	57		dB
Channel rejection, ±15MHz or more	Wanted signal at –82dBm, undesired signal is IEEE 802.15.4 modulated channel, stepped through all channels 2405MHz to 2480MHz, PER = 1%	59		dB
Blocking and desensitization, 5MHz from upper band edge	Wanted signal at –97dBm (3dB above the sensitivity level), CW jammer, PER = 1%	57		dB
Blocking and desensitization, 10MHz from upper band edge	Wanted signal at –97dBm (3dB above the sensitivity level), CW jammer, PER = 1%	63		dB
Blocking and desensitization, 20MHz from upper band edge	Wanted signal at –97dBm (3dB above the sensitivity level), CW jammer, PER = 1%	63		dB
Blocking and desensitization, 50MHz from upper band edge	Wanted signal at –97dBm (3dB above the sensitivity level), CW jammer, PER = 1%	66		dB
Blocking and desensitization, –5MHz from lower band edge	Wanted signal at –97dBm (3dB above the sensitivity level), CW jammer, PER = 1%	60		dB
Blocking and desensitization, –10MHz from lower band edge	Wanted signal at –97dBm (3dB above the sensitivity level), CW jammer, PER = 1%	60		dB
Blocking and desensitization, –20MHz from lower band edge	Wanted signal at –97dBm (3dB above the sensitivity level), CW jammer, PER = 1%	63		dB
Blocking and desensitization, –50MHz from lower band edge	Wanted signal at –97dBm (3dB above the sensitivity level), CW jammer, PER = 1%	65		dB
Spurious emissions, 30MHz to 1000MHz ⁽¹⁾	Measurement in a 50Ω single-ended load	-66		dBm
Spurious emissions, 1GHz to 12.75GHz ⁽¹⁾	Measurement in a 50Ω single-ended load	-53		dBm
Frequency error tolerance	Difference between the incoming carrier frequency and the internally generated carrier frequency	> 350		ppm
Symbol rate error tolerance	Difference between incoming symbol rate and the internally generated symbol rate	> 1000		ppm
RSSI dynamic range		95		dB
RSSI accuracy		±4		dB

⁽¹⁾ Suitable for systems targeting compliance with worldwide radio-frequency regulations ETSI EN 300 328 and EN 300 440 Class 2 (Europe), FCC CFR47 Part 15 (US), and ARIB STD-T66 (Japan)

Product Folder Links: CC2652P

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7.13 Zigbee and Thread—IEEE 802.15.4-2006 2.4GHz (OQPSK DSSS1:8, 250kbps): TX

Measured on the CC1352PEM-XD7793-XD24-PA24 reference design with T_c = 25°C, V_{DDS} = 3.0V, f_{RF} = 2440MHz with DC/DC enabled and high power PA connected to V_{DDS} unless otherwise noted.

All measurements are performed at the antenna input with a combined RX and TX path, except for high power PA which is measured at a dedicated antenna connection. All measurements are performed conducted.

PARAMETER		TEST CONDITIONS	MIN TYP	MAX	UNIT
General Parameters					
Max output power, high power PA	Differential mode, delivered to a si	ingle-ended 50Ω load through a balun	19.5		dBm
Output power programmable range, high power PA	Differential mode, delivered to a si	ingle-ended 50Ω load through a balun	6		dB
Max output power, high power PA, 10dBm configuration ⁽⁵⁾	Differential mode, delivered to a si	ingle-ended 50Ω load through a balun	10.5		dBm
Output power programmable range, high power PA, 10dBm configuration ⁽⁵⁾	Differential mode, delivered to a si	erential mode, delivered to a single-ended 50Ω load through a balun			dB
Max output power, regular PA	Differential mode, delivered to a si	ingle-ended 50Ω load through a balun	5		dBm
Output power programmable range, regular PA	Differential mode, delivered to a si	ingle-ended 50Ω load through a balun	26		dB
Spurious emissions and	harmonics				
Spurious emissions,	f < 1GHz, outside restricted bands		< –39		dBm
high-power PA ⁽¹⁾ (3)	f < 1GHz, restricted bands FCC		< -49		dBm
	f > 1GHz, including harmonics	+20dBm setting	-40		dBm
1 iai i i i i i i i i i i i i i i i i i	Second harmonic		-35		dBm
	Third harmonic		-42		dBm
	f < 1GHz, outside restricted bands		< -36		dBm
Spurious emissions, high-power PA, 10dBm	f < 1GHz, restricted bands ETSI		< -47		dBm
(1) (3) (5)	f < 1GHz, restricted bands FCC	+10dBm setting ⁽⁵⁾	< -55		dBm
	f > 1GHz, including harmonics	- roubin setting	-42		dBm
Harmonics,	Second harmonic		< -42		dBm
high-power PA, 10dBm configuration ^{(1) (5)}	Third harmonic		< -42		dBm
	f < 1GHz, outside restricted bands		< -36		dBm
Spurious emissions,	f < 1GHz, restricted bands ETSI		< -47		dBm
regular PA ⁽¹⁾ ⁽²⁾	f < 1GHz, restricted bands FCC	+5dBm setting	< -55		dBm
	f > 1GHz, including harmonics		< -42		dBm
Harmonics,	Second harmonic		< -42		dBm
regular PA (1)	Third harmonic		< -42		dBm
IEEE 802.15.4-2006 2.4GF	Hz (OQPSK DSSS1:8, 250kbps)				
Error vector magnitude, high power PA	+20dBm setting		2%		
Error vector magnitude, high power PA, 10dBm configuration ⁽⁵⁾	+10dBm setting		2%		
Error vector magnitude Regular PA	+5dBm setting		2%		

⁽¹⁾ Suitable for systems targeting compliance with worldwide radio-frequency regulations ETSI EN 300 328 and EN 300 440 Class 2 (Europe), FCC CFR47 Part 15 (US), and ARIB STD-T66 (Japan).



- (2) To ensure margins for passing FCC band edge requirements at 2483.5MHz, a lower than maximum output-power setting or less than 100% duty cycle may be used when operating at 2480MHz.
- (3) To ensure margins for passing FCC band edge requirements at 2483.5MHz, a lower than maximum output-power setting or less than 100% duty cycle may be used when operating at the upper 802.15.4 channel(s).
- (4) To ensure margins for passing FCC requirements for harmonic emission, duty cycling may be required. The CC1352P-2 LaunchPad reference design should also be reviewed as the filter provides higher attenuation of harmonics compared to the CC1352PEM-XD7793-XD24-PA24 reference design.
- (5) Measured on evaluation board as described in Optimizing the CC1352P and CC2652P for Coin Cell Operation at 10dBm Output Power

7.14 Timing and Switching Characteristics

7.14.1 Reset Timing

PARAMETER	MIN	TYP	MAX	UNIT
RESET_N low duration	1			μs

7.14.2 Wakeup Timing

Measured over operating free-air temperature with $V_{DDS} = 3.0V$ (unless otherwise noted). The times listed here do not include software overhead.

PARAMETER	TEST CONDITIONS	MIN	TYP MA	X UNIT
MCU, Reset to Active Timing		85	0 - 4000	μs
MCU, Shutdown to Active Timing ⁽¹⁾		85	0 - 4000	μs
MCU, Standby to Active			160	μs
MCU, Active to Standby			36	μs
MCU, Idle to Active			14	μs

⁽¹⁾ The wakeup time is dependent on remaining charge on VDDR capacitor when starting the device, and thus how long the device has been in Reset or Shutdown before starting up again. The wake up time increases with a higher capacitor value.

7.14.3 Clock Specifications

7.14.3.1 48MHz Crystal Oscillator (XOSC_HF)

Measured on a Texas Instruments reference design with $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted. (1)

	PARAMETER	MIN	TYP	MAX	UNIT
	Crystal frequency		48		MHz
ESR	Equivalent series resistance 6 pF < C _L ≤ 9 pF		20	60	Ω
ESR	Equivalent series resistance 5 pF < C _L ≤ 6 pF			80	Ω
L _M	Motional inductance, relates to the load capacitance that is used for the crystal (C _L in Farads) ⁽⁵⁾		< 3 × 10 ⁻²⁵ / C _L ²		Н
C _L	Crystal load capacitance ⁽⁴⁾	5	7 ⁽³⁾	9	pF
	Start-up time ⁽²⁾		200		μs

- (1) Probing or otherwise stopping the crystal while the DC/DC converter is enabled may cause permanent damage to the device.
- (2) Start-up time using the Ti-provided power driver. Start-up time may increase if driver is not used.
- (3) On-chip default connected capacitance including reference design parasitic capacitance. Connected internal capacitance is changed through software in the Customer Configuration section (CCFG).
- (4) Adjustable load capacitance is integrated into the device. External load capacitors are required for systems targeting compliance with certain regulations. See the device errata for further details.
- (5) The crystal manufacturer's specification must satisfy this requirement for proper operation.

7.14.3.2 48MHz RC Oscillator (RCOSC_HF)

Measured on a Texas Instruments reference design with $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

	MIN	TYP	MAX	UNIT
Frequency		48		MHz
Uncalibrated frequency accuracy		±1		%

Product Folder Links: CC2652P

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7.14.3.2 48MHz RC Oscillator (RCOSC_HF) (続き)

Measured on a Texas Instruments reference design with $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

	MIN	TYP	MAX	UNIT
Calibrated frequency accuracy ⁽¹⁾		±0.25		%
Start-up time		5		μs

(1) Accuracy relative to the calibration source (XOSC_HF)

7.14.3.3 2MHz RC Oscillator (RCOSC MF)

Measured on a Texas Instruments reference design with T_c = 25°C, V_{DDS} = 3.0V, unless otherwise noted.

	MIN	TYP	MAX	UNIT
Calibrated frequency		2		MHz
Start-up time		5		μs

7.14.3.4 32.768kHz Crystal Oscillator (XOSC LF)

Measured on a Texas Instruments reference design with T_c = 25°C, V_{DDS} = 3.0V, unless otherwise noted.

		MIN	TYP	MAX	UNIT
	Crystal frequency		32.768		kHz
ESR	Equivalent series resistance		30	100	kΩ
C _L	Crystal load capacitance	6	7 ⁽¹⁾	12	pF

 Default load capacitance using TI reference designs including parasitic capacitance. Crystals with different load capacitance may be used

7.14.3.5 32kHz RC Oscillator (RCOSC LF)

Measured on a Texas Instruments reference design with T_c = 25°C, V_{DDS} = 3.0V, unless otherwise noted.

	MIN	TYP	MAX	UNIT
Calibrated frequency		32.8 (1)		kHz
Temperature coefficient.		50		ppm/°C

(1) When using RCOSC_LF as source for the low frequency system clock (SCLK_LF), the accuracy of the SCLK_LF-derived Real Time Clock (RTC) can be improved by measuring RCOSC_LF relative to XOSC_HF and compensating for the RTC tick speed. This functionality is available through the TI-provided Power driver.

7.14.4 Synchronous Serial Interface (SSI) Characteristics

7.14.4.1 Synchronous Serial Interface (SSI) Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER NO.		PARAMETER	MIN	TYP	MAX	UNIT
S1	t _{clk_per}	SSICIk cycle time	12		65024	System Clocks (2)
S2 ⁽¹⁾	t _{clk_high}	SSICIk high time		0.5		t _{clk_per}
S3 ⁽¹⁾	t _{clk_low}	SSICIk low time		0.5		t _{clk_per}

(1) Refer to SSI timing diagrams Diagram 1, Diagram 2, Diagram 3

(2) When using the TI-provided Power driver, the SSI system clock is always 48MHz.

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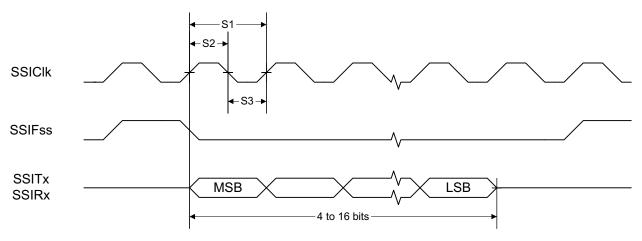


図 7-1. SSI Timing for TI Frame Format (FRF = 01), Single Transfer Timing Measurement

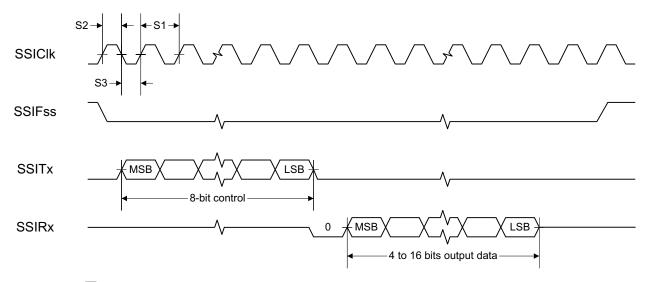


図 7-2. SSI Timing for MICROWIRE Frame Format (FRF = 10), Single Transfer

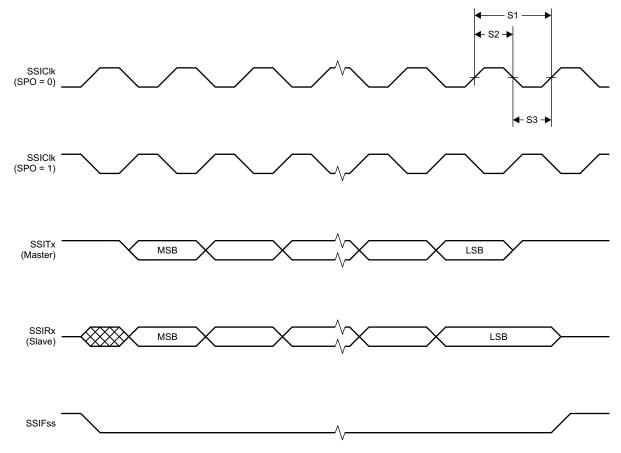


図 7-3. SSI Timing for SPI Frame Format (FRF = 00), With SPH = 1

7.14.5 UART

7.14.5.1 UART Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	MIN	TYP	MAX	UNIT
UART rate			3	MBaud



7.15 Peripheral Characteristics

7.15.1 ADC

7.15.1.1 Analog-to-Digital Converter (ADC) Characteristics

 T_c = 25°C, V_{DDS} = 3.0V and voltage scaling enabled, unless otherwise noted.⁽¹⁾ Performance numbers require use of offset and gain adjustements in software by TI-provided ADC drivers.

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
	Input voltage range		0	VDDS	V
	Resolution		12		Bits
	Sample Rate			200	ksps
	Offset	Internal 4.3V equivalent reference ⁽²⁾	-0.24		LSB
	Gain error	Internal 4.3V equivalent reference ⁽²⁾	7.14		LSB
DNL ⁽⁴⁾	Differential nonlinearity		>-1		LSB
INL	Integral nonlinearity		±4		LSB
		Internal 4.3V equivalent reference ⁽²⁾ , 200 kSamples/s, 9.6kHz input tone	9.8		
		Internal 4.3V equivalent reference ⁽²⁾ , 200 kSamples/s, 9.6kHz input tone, DC/DC enabled	9.8		
		VDDS as reference, 200 kSamples/s, 9.6kHz input tone	10.1		
ENOB	Effective number of bits	Internal reference, voltage scaling disabled, 32 samples average, 200 kSamples/s, 300 Hz input tone	11.1		Bits
		Internal reference, voltage scaling disabled, 14-bit mode, 200 kSamples/s, 600 Hz input tone (5)	11.3		
		Internal reference, voltage scaling disabled, 15-bit mode, 200 kSamples/s, 150 Hz input tone ⁽⁵⁾	11.6		
		Internal 4.3V equivalent reference ⁽²⁾ , 200 kSamples/s, 9.6kHz input tone	-65		
THD	Total harmonic distortion	VDDS as reference, 200 kSamples/s, 9.6kHz input tone	-70		dB
		Internal reference, voltage scaling disabled, 32 samples average, 200 kSamples/s, 300 Hz input tone	-72		
	Signal-to-noise	Internal 4.3V equivalent reference ⁽²⁾ , 200 kSamples/s, 9.6kHz input tone	60		
SINAD, SNDR	and	VDDS as reference, 200 kSamples/s, 9.6kHz input tone	63		dB
CHER	distortion ratio	Internal reference, voltage scaling disabled, 32 samples average, 200 kSamples/s, 300 Hz input tone	68		
		Internal 4.3V equivalent reference ⁽²⁾ , 200 kSamples/s, 9.6kHz input tone	70		
SFDR	Spurious-free dynamic range	VDDS as reference, 200 kSamples/s, 9.6kHz input tone	73		dB
		Internal reference, voltage scaling disabled, 32 samples average, 200 kSamples/s, 300 Hz input tone	75		
	Conversion time	Serial conversion, time-to-output, 24MHz clock	50		Clock Cycles
	Current consumption	Internal 4.3V equivalent reference ⁽²⁾	0.42		mA
	Current consumption	VDDS as reference	0.6		mA
	Reference voltage	Equivalent fixed internal reference (input voltage scaling enabled). For best accuracy, the ADC conversion should be initiated through the TI-RTOS API in order to include the gain/ offset compensation factors stored in FCFG1	4.3 ^{(2) (3)}		V
	Reference voltage	Fixed internal reference (input voltage scaling disabled). For best accuracy, the ADC conversion should be initiated through the TI-RTOS API in order to include the gain/offset compensation factors stored in FCFG1. This value is derived from the scaled value (4.3V) as follows: $V_{\text{ref}} = 4.3V \times 1408 / 4095$	1.48		V
	Reference voltage	VDDS as reference, input voltage scaling enabled	VDDS		V
	Reference voltage	VDDS as reference, input voltage scaling disabled	VDDS / 2.82 ⁽³⁾		V

Product Folder Links: CC2652P

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7.15.1.1 Analog-to-Digital Converter (ADC) Characteristics (続き)

 T_c = 25°C, V_{DDS} = 3.0V and voltage scaling enabled, unless otherwise noted.⁽¹⁾

Performance numbers require use of offset and gain adjustements in software by TI-provided ADC drivers.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
1		200 kSamples/s, voltage scaling enabled. Capacitive input, Input impedance depends on sampling frequency and sampling time		>1		ΜΩ

- (1) Using IEEE Std 1241-2010 for terminology and test methods
- (2) Input signal scaled down internally before conversion, as if voltage range was 0 to 4.3V
- (3) Applied voltage must be within Absolute Maximum Ratings (see セクション 7.1) at all times
- (4) No missing codes
- (5) ADC_output = $\Sigma(4^n \text{ samples }) >> n, n = \text{desired extra bits}$

7.15.2 DAC

7.15.2.1 Digital-to-Analog Converter (DAC) Characteristics

 $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Genera	l Parameters					
	Resolution			8		Bits
		Any load, any V _{REF} , precharge OFF, DAC charge-pump ON	1.8		3.8	
V_{DDS}	Supply voltage	External Load ⁽⁴⁾ , any V _{REF} , precharge OFF, DAC charge-pump OFF	2.0		3.8	V
		Any load, V _{REF} = DCOUPL, precharge ON	2.6		3.8	
-	Clask fraguency	Buffer ON (recommended for external load)	16		250	kHz
F _{DAC}	Clock frequency	Buffer OFF (internal load)	16		1000	KHZ
	Valtage output settling time	V _{REF} = VDDS, buffer OFF, internal load		13		1/5
	Voltage output settling time	V _{REF} = VDDS, buffer ON, external capacitive load = 20pF ⁽³⁾		13.8		1 / F _{DAC}
	External capacitive load			20	200	pF
	External resistive load		10			ΜΩ
	Short circuit current				400	μA
		VDDS = 3.8V, DAC charge-pump OFF		50.8		
	Max output impedance Vref = VDDS, buffer ON, CLK	VDDS = 3.0V, DAC charge-pump ON		51.7		
		VDDS = 3.0V, DAC charge-pump OFF		53.2		
Z _{MAX}		VDDS = 2.0V, DAC charge-pump ON		48.7		kΩ
	250kHz ⁽⁵⁾	VDDS = 2.0V, DAC charge-pump OFF		70.2		
		VDDS = 1.8V, DAC charge-pump ON		46.3		
		VDDS = 1.8V, DAC charge-pump OFF		88.9		
Internal	Load - Continuous Time Com	parator / Low Power Clocked Comparator			1	
DAII	Differential nonlinearity	V _{REF} = VDDS, load = Continuous Time Comparator or Low Power Clocked Comparator F _{DAC} = 250kHz		±1		LSB ⁽¹⁾
DNL	Differential nonlinearity	V _{REF} = VDDS, load = Continuous Time Comparator or Low Power Clocked Comparator F _{DAC} = 16kHz		±1.2		LSB
		V _{REF} = VDDS = 3.8V		±0.64		
		V _{REF} = VDDS= 3.0V		±0.81		
	Offset error ⁽²⁾ Load = Continuous Time	V _{REF} = VDDS = 1.8V		±1.27		LSB ⁽¹⁾
	Comparator	V _{REF} = DCOUPL, precharge ON		±3.43		LOD
		V _{REF} = DCOUPL, precharge OFF		±2.88		
		V _{REF} = ADCREF		±2.37		



7.15.2.1 Digital-to-Analog Converter (DAC) Characteristics (続き)

 $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

	PARAMETER	TEST CONDITIONS	MIN TYP M	AX UNIT
		V _{REF} = VDDS= 3.8V	±0.78	
	Offset error ⁽²⁾ Load = Low Power Clocked	V _{REF} = VDDS = 3.0V	±0.77	
	=	V _{REF} = VDDS= 1.8V	±3.46	LSB ⁽¹⁾
	Comparator	V _{REF} = DCOUPL, precharge ON	±3.44	LOD
		V _{REF} = DCOUPL, precharge OFF	±4.70	
		V _{REF} = ADCREF	±4.11	
	Max code output voltage variation ⁽²⁾ Load = Continuous Time Comparator	V _{REF} = VDDS = 3.8V	±1.53	
		V _{REF} = VDDS = 3.0V	±1.71	
		V _{REF} = VDDS= 1.8V	±2.10	LSB ⁽¹⁾
		V _{REF} = DCOUPL, precharge ON	±6.00	LSB()
	Comparator	V _{REF} = DCOUPL, precharge OFF	±3.85	
		V _{REF} = ADCREF	±5.84	
		V _{REF} = VDDS= 3.8V	±2.92	
	Max code output voltage	V _{REF} =VDDS= 3.0V	±3.06	
	variation ⁽²⁾	V _{REF} = VDDS= 1.8V	±3.91	L CD(1)
	Load = Low Power Clocked	V _{REF} = DCOUPL, precharge ON	±7.84	LSB ⁽¹⁾
	Comparator	V _{REF} = DCOUPL, precharge OFF	±4.06	
		V _{REF} = ADCREF	±6.94	
		V _{REF} = VDDS = 3.8V, code 1	0.03	
		V _{REF} = VDDS = 3.8V, code 255	3.62	
		V _{REF} = VDDS= 3.0V, code 1	0.02	
		V _{REF} = VDDS= 3.0V, code 255	2.86	
		V _{REF} = VDDS= 1.8V, code 1	0.01	
	Output voltage range ⁽²⁾	V _{REF} = VDDS = 1.8V, code 255	1.71	.,
	Load = Continuous Time Comparator	V _{REF} = DCOUPL, precharge OFF, code 1	0.01	V
		V _{REF} = DCOUPL, precharge OFF, code 255	1.21	
		V _{REF} = DCOUPL, precharge ON, code 1	1.27	
		V _{REF} = DCOUPL, precharge ON, code 255	2.46	
		V _{REF} = ADCREF, code 1	0.01	
		V _{REF} = ADCREF, code 255	1.41	
		V _{REF} = VDDS = 3.8V, code 1	0.03	
		V _{REF} = VDDS= 3.8V, code 255	3.61	
		V _{REF} = VDDS= 3.0V, code 1	0.02	
		V _{REF} = VDDS= 3.0V, code 255	2.85	
		V _{REF} = VDDS = 1.8V, code 1	0.01	
	Output voltage range ⁽²⁾	V _{REF} = VDDS = 1.8V, code 255	1.71	
	Load = Low Power Clocked Comparator	V _{REF} = DCOUPL, precharge OFF, code 1	0.01	V
	Comparator	V _{REF} = DCOUPL, precharge OFF, code 255	1.21	
		V _{REF} = DCOUPL, precharge ON, code 1	1.27	
		V _{REF} = DCOUPL, precharge ON, code 255	2.46	
		V _{REF} = ADCREF, code 1	0.01	
		V _{REF} = ADCREF, code 255	1.41	
ternal	Load (Keysight 34401A Multi			
	(, , , , , , , , , , , , , , , , , , ,	V _{REF} = VDDS, F _{DAC} = 250kHz	±1	
_	Integral nonlinearity	V _{REF} = DCOUPL, F _{DAC} = 250kHz	±1	LSB ⁽¹⁾
	g	V _{REF} = ADCREF, F _{DAC} = 250kHz	±1	
IL	Differential nonlinearity	V _{REF} = VDDS, F _{DAC} = 250kHz	±1	LSB ⁽¹⁾

7.15.2.1 Digital-to-Analog Converter (DAC) Characteristics (続き)

 $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
DAC Offset error	V _{REF} = VDDS= 3.8V	±0.40		
	V _{REF} = VDDS= 3.0V	±0.50		
	V _{REF} = VDDS = 1.8V	±0.75		LSB ⁽¹
	V _{REF} = DCOUPL, precharge ON	±1.55		LOB(.
	V _{REF} = DCOUPL, precharge OFF	±1.30		
	V _{REF} = ADCREF	±1.10		
	V _{REF} = VDDS= 3.8V	±1.00		
	V _{REF} = VDDS= 3.0V	±1.00		
DAC Max code output	V _{REF} = VDDS= 1.8V	±1.00		LSB ⁽¹
voltage variation	V _{REF} = DCOUPL, precharge ON	±3.45		LSB
	V _{REF} = DCOUPL, precharge OFF	±2.10		
	V _{REF} = ADCREF	±1.90		
	V _{REF} = VDDS = 3.8V, code 1	0.03		
	V _{REF} = VDDS = 3.8V, code 255	3.61		
	V _{REF} = VDDS = 3.0V, code 1	0.02		
	V _{REF} = VDDS= 3.0V, code 255	2.85		
	V _{REF} = VDDS= 1.8V, code 1	0.02		
Output voltage range Load = Low Power Clocked	V _{REF} = VDDS = 1.8V, code 255	1.71		V
Comparator	V _{REF} = DCOUPL, precharge OFF, code 1	0.02		V
	V _{REF} = DCOUPL, precharge OFF, code 255	1.20		
	V _{REF} = DCOUPL, precharge ON, code 1	1.27		
	V _{REF} = DCOUPL, precharge ON, code 255	2.46		
	V _{REF} = ADCREF, code 1	0.02		
	V _{REF} = ADCREF, code 255	1.42		

¹ LSB (V_{REF} 3.8V/3.0V/1.8V/DCOUPL/ADCREF) = 14.10mV/11.13mV/6.68mV/4.67mV/5.48mV

⁽²⁾ (3) Includes comparator offset

A load > 20pF will increase the settling time

Keysight 34401A Multimeter

⁽⁴⁾ (5) When using lower levels of VDDS with the charge pump OFF, care must be taken to adapt the surrounding circuit to the increase in impedance.



7.15.3 Temperature and Battery Monitor

7.15.3.1 Temperature Sensor

Measured on a Texas Instruments reference design with $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Resolution			2		°C
Accuracy	-40 °C to 0 °C		±4.0		°C
Accuracy	0 °C to 85°C		±2.5		°C
Supply voltage coefficient ⁽¹⁾			3.6		°C/V

⁽¹⁾ The temperature sensor is automatically compensated for VDDS variation when using the TI-provided driver.

7.15.3.2 Battery Monitor

Measured on a Texas Instruments reference design with T_c = 25°C, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Resolution			25		mV
Range		1.8		3.8	V
Integral nonlinearity (max)			23		mV
Accuracy	VDDS = 3.0V		22.5		mV
Offset error			-32		mV
Gain error			-1		%

Product Folder Links: CC2652P

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7.15.4 Comparators

7.15.4.1 Low-Power Clocked Comparator

 $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input voltage range		0		V _{DDS}	V
Clock frequency		SCLK_LF			
Internal reference voltage ⁽¹⁾	Using internal DAC with VDDS as reference voltage, DAC code = 0 - 255	0.024 - 2.865			V
Offset	Measured at V _{DDS} / 2, includes error from internal DAC	±5		mV	
Decision time	Step from –50mV to 50mV	1			Clock Cycle

⁽¹⁾ The comparator can use an internal 8 bits DAC as its reference. The DAC output voltage range depends on the reference voltage selected. See セクション 7.15.2.1

7.15.4.2 Continuous Time Comparator

 T_c = 25°C, V_{DDS} = 3.0V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input voltage range ⁽¹⁾		0		V_{DDS}	V
Offset	Measured at V _{DDS} / 2		±5		mV
Decision time	Step from -10mV to 10mV		0.78		μs
Current consumption	Internal reference		8.6		μA

⁽¹⁾ The input voltages can be generated externally and connected throughout I/Os or an internal reference voltage can be generated using the DAC

7.15.5 Current Source

7.15.5.1 Programmable Current Source

 $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Current source programmable output range (logarithmic range)			0.25 - 20		μΑ
Resolution			0.25		μΑ



7.15.6 GPIO

7.15.6.1 GPIO DC Characteristics

PARAMETER	TEST CONDITIONS	MIN	TYP MAX	UNIT
T _A = 25°C, V _{DDS} = 1.8V				
GPIO VOH at 8 mA load	IOCURR = 2, high-drive GPIOs only		1.56	V
GPIO VOL at 8 mA load	IOCURR = 2, high-drive GPIOs only		0.24	V
GPIO VOH at 4 mA load	IOCURR = 1		1.59	V
GPIO VOL at 4 mA load	IOCURR = 1		0.21	V
GPIO pullup current	Input mode, pullup enabled, Vpad = 0V		73	μA
GPIO pulldown current	Input mode, pulldown enabled, Vpad = VDDS		19	μA
GPIO low-to-high input transition, with hysteresis	IH = 1, transition voltage for input read as $0 \rightarrow 1$		1.08	V
GPIO high-to-low input transition, with hysteresis	IH = 1, transition voltage for input read as $1 \rightarrow 0$		0.73	V
GPIO input hysteresis	IH = 1, difference between $0 \rightarrow 1$ and $1 \rightarrow 0$ points		0.35	V
T _A = 25°C, V _{DDS} = 3.0V				
GPIO VOH at 8 mA load	IOCURR = 2, high-drive GPIOs only		2.59	V
GPIO VOL at 8 mA load	IOCURR = 2, high-drive GPIOs only		0.42	V
GPIO VOH at 4 mA load	IOCURR = 1		2.63	V
GPIO VOL at 4 mA load	IOCURR = 1		0.40	V
T _A = 25°C, V _{DDS} = 3.8V				
GPIO pullup current	Input mode, pullup enabled, Vpad = 0V		282	μA
GPIO pulldown current	Input mode, pulldown enabled, Vpad = VDDS		110	μA
GPIO low-to-high input transition, with hysteresis	IH = 1, transition voltage for input read as $0 \rightarrow 1$		1.97	V
GPIO high-to-low input transition, with hysteresis	IH = 1, transition voltage for input read as $1 \rightarrow 0$		1.55	V
GPIO input hysteresis	IH = 1, difference between $0 \rightarrow 1$ and $1 \rightarrow 0$ points		0.42	V
T _A = 25°C				
VIH	Lowest GPIO input voltage reliably interpreted as a High	0.8*V _{DDS}		V
VIL	Highest GPIO input voltage reliably interpreted as a Low		0.2*V _{DD\$}	y V

7.16 Typical Characteristics

All measurements in this section are done with T_c = 25°C and V_{DDS} = 3.0V, unless otherwise noted. See *Recommended Operating Conditions* for device limits. Values exceeding these limits are for reference only.

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7.16.1 MCU Current

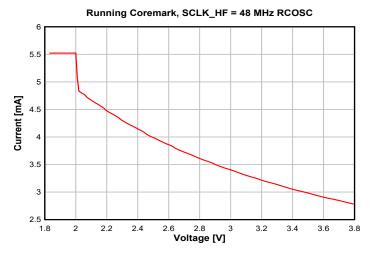
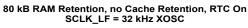


図 7-4. Active Mode (MCU) Current vs. Supply Voltage (VDDS)



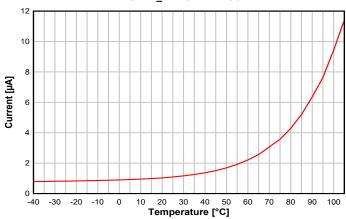


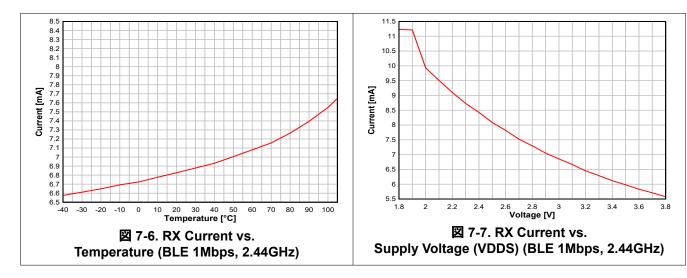
図 7-5. Standby Mode (MCU) Current vs. Temperature

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7.16.2 RX Current



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7.16.3 TX Current

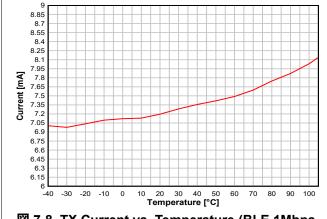


図 7-8. TX Current vs. Temperature (BLE 1Mbps, 2.44GHz, 0dBm)

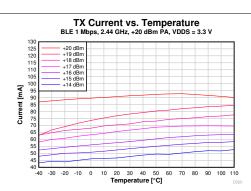


図 7-9. TX Current vs. Temperature (BLE 1Mbps, 2.44GHz, VDDS = 3.3V)

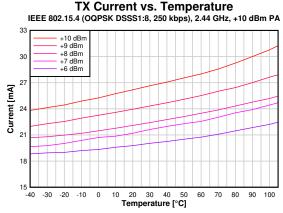
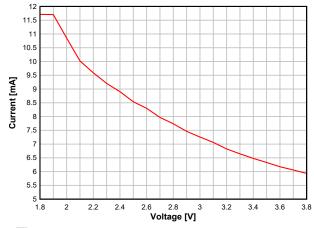
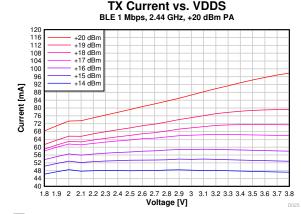
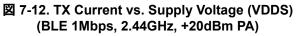


図 7-10. TX Current vs. Temperature (250kbps, 2.44GHz, +10dBm PA)



☑ 7-11. TX Current vs. Supply Voltage (VDDS)
(BLE 1Mbps, 2.44GHz, 0dBm)





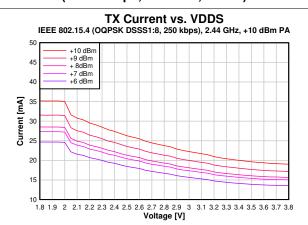


図 7-13. TX Current vs. Supply Voltage (VDDS) (250kbps, 2.44GHz, +10dBm PA)

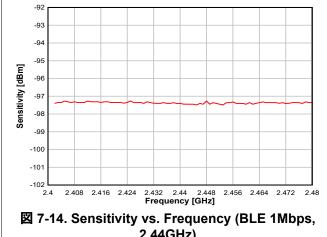


表 7-1 shows typical TX current and output power for different output power settings.

表 7-1. Typical TX Current and Output Power

	CC2652P at 2.4GHz, VDDS = 3.0V (Measured on CC1352PEM-XD7793-XD24-PA24)					
txPower	TX Power Setting (SmartRF Studio)	Typical Output Power [dBm]	Typical Current Consumption [mA]			
0x7217	5	3.1	8.7			
0x4E63	4	1.8	8.2			
0x385D	3	0.5	7.7			
0x3259	2	-0.7	7.3			
0x2856	1	-1.8	6.9			
0x2853	0	-3.1	6.6			
0x12D6	-5	-7.7	5.8			
0x0ACF	-10	-12.6	5.3			
0x06CA	-15	-17.9	4.9			
0x04C6	-20	-23.6	4.7			

7.16.4 RX Performance



2.44GHz)

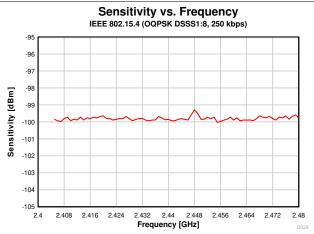


図 7-15. Sensitivity vs. Frequency (IEEE 802.15.4-2006, 250 kbps, OQPSK DSSS 1:8, 2.44GHz)

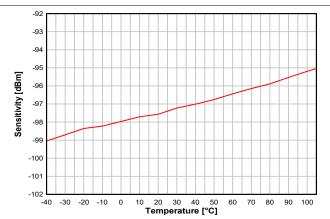


図 7-16. Sensitivity vs. Temperature (BLE 1Mbps, 2.44GHz)

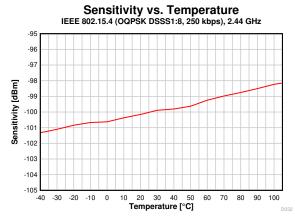
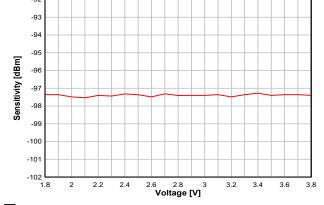


図 7-17. Sensitivity vs. Temperature (IEEE 802.15.4-2006, 250 kbps, OQPSK DSSS 1:8, 2.44GHz)



1Mbps, 2.44GHz)

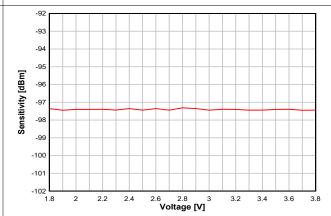
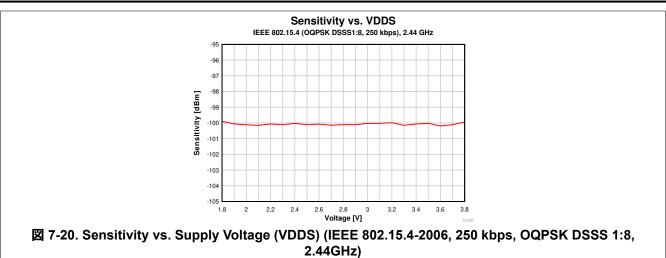
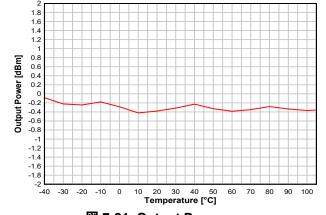


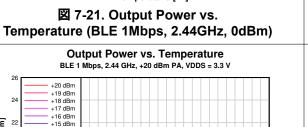
図 7-18. Sensitivity vs. Supply Voltage (VDDS) (BLE 図 7-19. Sensitivity vs. Supply Voltage (VDDS) (BLE 1Mbps, 2.44GHz, DCDC Off)





7.16.5 TX Performance





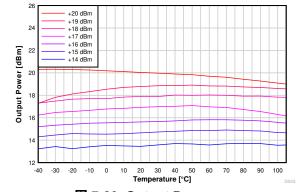


図 7-23. Output Power vs.
Temperature (BLE 1Mbps, 2.44GHz, +20dBm PA)

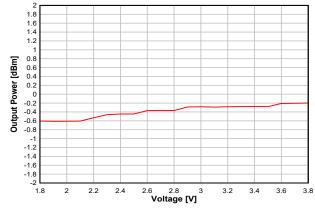
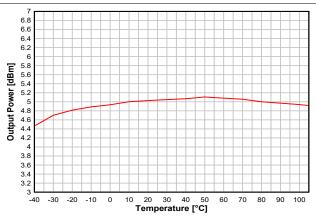


図 7-25. Output Power vs.
Supply Voltage (VDDS) (BLE 1 Mbps, 2.44GHz, 0dBm)



☑ 7-22. Output Power vs.
Temperature (BLE 1Mbps, 2.44GHz, +5dBm)

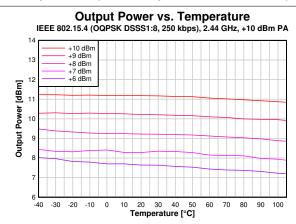


図 7-24. Output Power vs.
Temperature (IEEE 802.15.4-2006, 250 kbps, OQPSK DSSS 1:8, 2.44GHz, +10dBm PA)

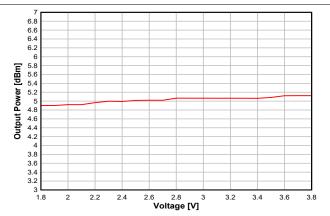
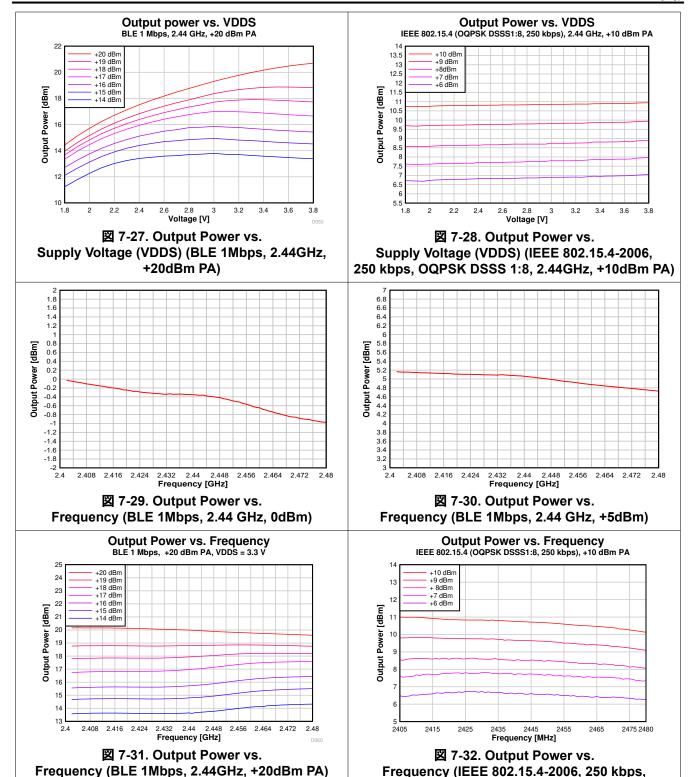


図 7-26. Output Power vs.
Supply Voltage (VDDS) (BLE 1 Mbps, 2.44GHz, +5dBm)



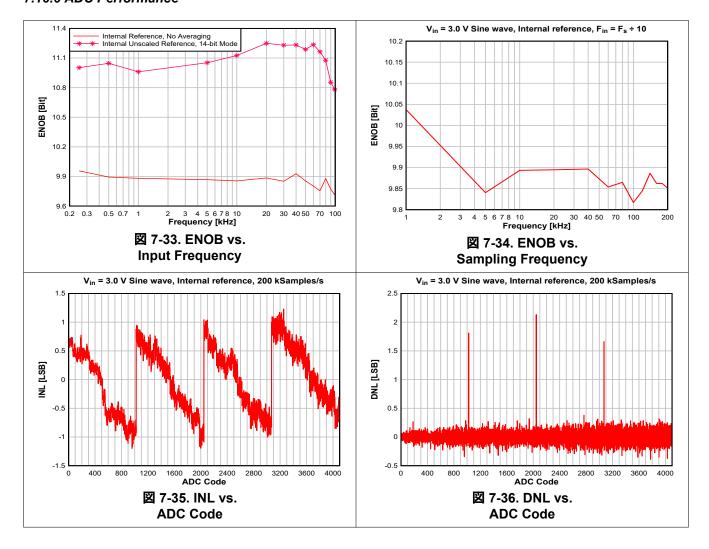


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OQPSK DSSS 1:8, 2.44GHz, +10dBm PA)

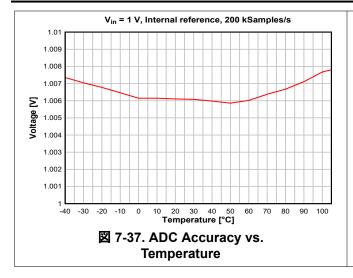


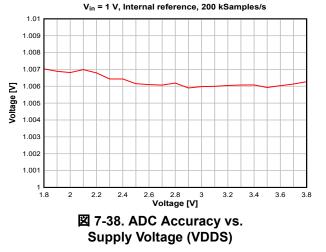
7.16.6 ADC Performance



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8 Detailed Description

8.1 Overview

セクション 4 shows the core modules of the CC2652P device.

8.2 System CPU

The CC2652P SimpleLink[™] Wireless MCU contains an Arm[®] Cortex[®]-M4F system CPU, which runs the application and the higher layers of radio protocol stacks.

The system CPU is the foundation of a high-performance, low-cost platform that meets the system requirements of minimal memory implementation, and low-power consumption, while delivering outstanding computational performance and exceptional system response to interrupts.

Its features include the following:

- · ARMv7-M architecture optimized for small-footprint embedded applications
- Arm Thumb®-2 mixed 16- and 32-bit instruction set delivers the high performance expected of a 32-bit Arm
 core in a compact memory size
- · Fast code execution permits increased sleep mode time
- Deterministic, high-performance interrupt handling for time-critical applications
- · Single-cycle multiply instruction and hardware divide
- · Hardware division and fast digital-signal-processing oriented multiply accumulate
- Saturating arithmetic for signal processing
- IEEE 754-compliant single-precision Floating Point Unit (FPU)
- · Memory Protection Unit (MPU) for safety-critical applications
- Full debug with data matching for watchpoint generation
 - Data Watchpoint and Trace Unit (DWT)
 - JTAG Debug Access Port (DAP)
 - Flash Patch and Breakpoint Unit (FPB)
- Trace support reduces the number of pins required for debugging and tracing
 - Instrumentation Trace Macrocell Unit (ITM)
 - Trace Port Interface Unit (TPIU) with asynchronous serial wire output (SWO)
- Optimized for single-cycle flash memory access
- Tightly connected to 8kB 4-way random replacement cache for minimal active power consumption and wait states
- Ultra-low-power consumption with integrated sleep modes
- 48MHz operation
- 1.25 DMIPS per MHz

8.3 Radio (RF Core)

The RF Core is a highly flexible and future proof radio module which contains an Arm Cortex-M0 processor that interfaces the analog RF and base-band circuitry, handles data to and from the system CPU side, and assembles the information bits in a given packet structure. The RF core offers a high level, command-based API to the main CPU that configurations and data are passed through. The Arm Cortex-M0 processor is not programmable by customers and is interfaced through the TI-provided RF driver that is included with the SimpleLink Software Development Kit (SDK).

The RF core can autonomously handle the time-critical aspects of the radio protocols, thus offloading the main CPU, which reduces power and leaves more resources for the user application. Several signals are also available to control external circuitry such as RF switches or range extenders autonomously.

Multiprotocol solutions are enabled through time-sliced access of the radio, handled transparently for the application through the TI-provided RF driver and dual-mode manager.

A Packet Traffic Arbitrator (PTA) scheme is available for the managed coexistence of BLE and a co-located 2.4GHz radio. This is based on 802.15.2 recommendations and common industry standards. The 3-wire coexistence interface has multiple modes of operation, encompassing different use cases and number of lines used for signaling. The radio acting as a slave is able to request access to the 2.4GHz ISM band, and the master to grant it. Information about the request priority and TX or RX operation can also be conveyed.

The various physical layer radio formats are partly built as a software defined radio where the radio behavior is either defined by radio ROM contents or by non-ROM radio formats delivered in form of firmware patches with the SimpleLink SDKs. This allows the radio platform to be updated for support of future versions of standards even with over-the-air (OTA) updates while still using the same silicon.

8.3.1 Bluetooth 5.2 Low Energy

The RF Core offers full support for Bluetooth 5.2 Low Energy, including the high-speed 2Mbps physical layer and the 500kbps and 125kbps long range PHYs (Coded PHY) through the TI provided Bluetooth 5.2 stack or through a high-level Bluetooth API. The Bluetooth 5.2 PHY and part of the controller are in radio and system ROM, providing significant savings in memory usage and more space available for applications.

The new high-speed mode allows data transfers up to 2Mbps, twice the speed of Bluetooth 4.2 and five times the speed of Bluetooth 4.0, without increasing power consumption. In addition to faster speeds, this mode offers significant improvements for energy efficiency and wireless coexistence with reduced radio communication time.

Bluetooth 5.2 also enables unparalleled flexibility for adjustment of speed and range based on application needs, which capitalizes on the high-speed or long-range modes respectively. Data transfers are now possible at 2Mbps, enabling development of applications using voice, audio, imaging, and data logging that were not previously an option using Bluetooth low energy. With high-speed mode, existing applications deliver faster responses, richer engagement, and longer battery life. Bluetooth 5.2 enables fast, reliable firmware updates.

8.3.2 802.15.4 (Thread, Zigbee, 6LoWPAN)

Through a dedicated IEEE radio API, the RF Core supports the 2.4GHz IEEE 802.15.4-2011 physical layer (2 Mchips per second Offset-QPSK with DSSS 1:8), used in Thread, Zigbee, and 6LoWPAN protocols. The 802.15.4 PHY and MAC are in radio and system ROM. TI also provides royalty-free protocol stacks for Thread and Zigbee as part of the SimpleLink SDK, enabling a robust end-to-end solution.

8.4 Memory

Up to 352kB nonvolatile (Flash) memory provides storage for code and data. The flash memory is in-system programmable and erasable. The last flash memory sector must contain a Customer Configuration section (CCFG) that is used by boot ROM and TI provided drivers to configure the device. This configuration is done through the ccfg.c source file that is included in all TI provided examples.

The ultra-low leakage system static RAM (SRAM) is split into up to five 16kB blocks and can be used for both storage of data and execution of code. Retention of SRAM contents in Standby power mode is enabled by

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default and included in Standby mode power consumption numbers. Parity checking for detection of bit errors in memory is built-in, which reduces chip-level soft errors and thereby increases reliability. System SRAM is always initialized to zeroes upon code execution from boot.

To improve code execution speed and lower power when executing code from nonvolatile memory, a 4-way nonassociative 8kB cache is enabled by default to cache and prefetch instructions read by the system CPU. The cache can be used as a general-purpose RAM by enabling this feature in the Customer Configuration Area (CCFG).

There is a 4kB ultra-low leakage SRAM available for use with the Sensor Controller Engine which is typically used for storing Sensor Controller programs, data and configuration parameters. This RAM is also accessible by the system CPU. The Sensor Controller RAM is not cleared to zeroes between system resets.

The ROM includes a TI-RTOS kernel and low-level drivers, as well as significant parts of selected radio stacks, which frees up flash memory for the application. The ROM also contains a serial (SPI and UART) bootloader that can be used for initial programming of the device.

8.5 Sensor Controller

The Sensor Controller contains circuitry that can be selectively enabled in both Standby and Active power modes. The peripherals in this domain can be controlled by the Sensor Controller Engine, which is a proprietary power-optimized CPU. This CPU can read and monitor sensors or perform other tasks autonomously; thereby significantly reducing power consumption and offloading the system CPU.

The Sensor Controller Engine is user programmable with a simple programming language that has syntax similar to C. This programmability allows for sensor polling and other tasks to be specified as sequential algorithms rather than static configuration of complex peripheral modules, timers, DMA, register programmable state machines, or event routing.

The main advantages are:

- Flexibility—Data can be read and processed in unlimited manners while still ensuring ultra-low power.
- 2MHz low-power mode enables lowest possible handling of digital sensors.
- Dvnamic reuse of hardware resources
- · 40-bit accumulator supporting multiplication, addition and shift
- · Observability and debugging options

Sensor Controller Studio is used to write, test, and debug code for the Sensor Controller. The tool produces C driver source code, which the System CPU application uses to control and exchange data with the Sensor Controller. Typical use cases may be (but are not limited to) the following:

- Read analog sensors using integrated ADC or comparators
- Interface digital sensors using GPIOs, SPI, UART, or I²C (UART and I²C are bit-banged)
- · Capacitive sensing
- Waveform generation
- Very low-power pulse counting (flow metering)
- Key scan

The peripherals in the Sensor Controller include the following:

- The low-power clocked comparator can be used to wake the system CPU from any state in which the comparator is active. A configurable internal reference DAC can be used in conjunction with the comparator. The output of the comparator can also be used to trigger an interrupt or the ADC.
- Capacitive sensing functionality is implemented through the use of a constant current source, a time-to-digital
 converter, and a comparator. The continuous time comparator in this block can also be used as a higheraccuracy alternative to the low-power clocked comparator. The Sensor Controller takes care of baseline
 tracking, hysteresis, filtering, and other related functions when these modules are used for capacitive
 sensing.
- The ADC is a 12-bit, 200 ksamples/s ADC with eight inputs and a built-in voltage reference. The ADC can be triggered by many different sources including timers, I/O pins, software, and comparators.

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- The analog modules can connect to up to eight different GPIOs.
- Dedicated SPI master with up to 6MHz clock speed

The peripherals in the Sensor Controller can also be controlled from the main application processor.

8.6 Cryptography

The CC2652P device comes with a wide set of modern cryptography-related hardware accelerators, drastically reducing code footprint and execution time for cryptographic operations. It also has the benefit of being lower power and improves availability and responsiveness of the system because the cryptography operations runs in a background hardware thread.

Together with a large selection of open-source cryptography libraries provided with the Software Development Kit (SDK), this allows for secure and future proof IoT applications to be easily built on top of the platform. The hardware accelerator modules are:

- True Random Number Generator (TRNG) module provides a true, nondeterministic noise source for the purpose of generating keys, initialization vectors (IVs), and other random number requirements. The TRNG is built on 24 ring oscillators that create unpredictable output to feed a complex nonlinear-combinatorial circuit.
- Secure Hash Algorithm 2 (SHA-2) with support for SHA224, SHA256, SHA384, and SHA512
- Advanced Encryption Standard (AES) with 128 and 256 bit key lengths
- **Public Key Accelerator** Hardware accelerator supporting mathematical operations needed for elliptic curves up to 512 bits and RSA key pair generation up to 1024 bits.

Through use of these modules and the TI provided cryptography drivers, the following capabilities are available for an application or stack:

Key Agreement Schemes

- Elliptic curve Diffie–Hellman with static or ephemeral keys (ECDH and ECDHE)
- Elliptic curve Password Authenticated Key Exchange by Juggling (ECJ-PAKE)

Signature Generation

Elliptic curve Diffie-Hellman Digital Signature Algorithm (ECDSA)

Curve Support

- Short Weierstrass form (full hardware support), such as:
 - NIST-P224, NIST-P256, NIST-P384, NIST-P521
 - Brainpool-256R1, Brainpool-384R1, Brainpool-512R1
 - secp256r1
- Montgomery form (hardware support for multiplication), such as:
 - Curve25519

SHA2 based MACs

- HMAC with SHA224, SHA256, SHA384, or SHA512
- Block cipher mode of operation
 - AESCCM
 - AESGCM
 - AESECB
 - AESCBC
 - AESCBC-MAC

True random number generation

Other capabilities, such as RSA encryption and signatures as well as Edwards type of elliptic curves such as Curve1174 or Ed25519, can also be implemented using the provided hardware accelerators but are not part of the TI SimpleLink SDK for the CC2652P device.

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8.7 Timers

A large selection of timers are available as part of the CC2652P device. These timers are:

Real-Time Clock (RTC)

A 70-bit 3-channel timer running on the 32kHz low frequency system clock (SCLK_LF). This timer is available in all power modes except Shutdown. The timer can be calibrated to compensate for frequency drift when using the LF RCOSC as the low frequency system clock. If an external LF clock with frequency different from 32.768kHz is used, the RTC tick speed can be adjusted to compensate for this. When using TI-RTOS, the RTC is used as the base timer in the operating system and should thus only be accessed through the kernel APIs such as the Clock module. The real time clock can also be read by the Sensor Controller Engine to timestamp sensor data and also has dedicated capture channels. By default, the RTC halts when a debugger halts the device.

General Purpose Timers (GPTIMER)

The four flexible GPTIMERs can be used as either 4× 32 bit timers or 8× 16 bit timers, all running on up to 48MHz. Each of the 16- or 32-bit timers support a wide range of features such as one-shot or periodic counting, pulse width modulation (PWM), time counting between edges and edge counting. The inputs and outputs of the timer are connected to the device event fabric, which allows the timers to interact with signals such as GPIO inputs, other timers, DMA and ADC. The GPTIMERs are available in Active and Idle power modes.

Sensor Controller Timers

The Sensor Controller contains 3 timers:

AUX Timer 0 and 1 are 16-bit timers with a 2^N prescaler. Timers can either increment on a clock or on each edge of a selected tick source. Both one-shot and periodical timer modes are available.

AUX Timer 2 is a 16-bit timer that can operate at 24MHz, 2MHz or 32kHz independent of the Sensor Controller functionality. There are 4 capture or compare channels, which can be operated in one-shot or periodical modes. The timer can be used to generate events for the Sensor Controller Engine or the ADC, as well as for PWM output or waveform generation.

Radio Timer

A multichannel 32-bit timer running at 4MHz is available as part of the device radio. The radio timer is typically used as the timing base in wireless network communication using the 32-bit timing word as the network time. The radio timer is synchronized with the RTC by using a dedicated radio API when the device radio is turned on or off. This ensures that for a network stack, the radio timer seems to always be running when the radio is enabled. The radio timer is in most cases used indirectly through the trigger time fields in the radio APIs and should only be used when running the accurate 48MHz high frequency crystal is the source of SCLK_HF.

Watchdog timer

The watchdog timer is used to regain control if the system operates incorrectly due to software errors. It is typically used to generate an interrupt to and reset of the device for the case where periodic monitoring of the system components and tasks fails to verify proper functionality. The watchdog timer runs on a 1.5MHz clock rate and cannot be stopped once enabled. The watchdog timer pauses to run in Standby power mode and when a debugger halts the device.

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8.8 Serial Peripherals and I/O

The SSIs are synchronous serial interfaces that are compatible with SPI, MICROWIRE, and TI's synchronous serial interfaces. The SSIs support both SPI master and slave up to 4MHz. The SSI modules support configurable phase and polarity.

The UARTs implement universal asynchronous receiver and transmitter functions. They support flexible baudrate generation up to a maximum of 3Mbps.

The I²S interface is used to handle digital audio and can also be used to interface pulse-density modulation microphones (PDM).

The I²C interface is also used to communicate with devices compatible with the I²C standard. The I²C interface can handle 100kHz and 400kHz operation, and can serve as both master and slave.

The I/O controller (IOC) controls the digital I/O pins and contains multiplexer circuitry to allow a set of peripherals to be assigned to I/O pins in a flexible manner. All digital I/Os are interrupt and wake-up capable, have a programmable pullup and pulldown function, and can generate an interrupt on a negative or positive edge (configurable). When configured as an output, pins can function as either push-pull or open-drain. Five GPIOs have high-drive capabilities, which are marked in **bold** in セクション 6. All digital peripherals can be connected to any digital pin on the device.

For more information, see the CC13x2, CC26x2 SimpleLink™ Wireless MCU Technical Reference Manual.

8.9 Battery and Temperature Monitor

A combined temperature and battery voltage monitor is available in the CC2652P device. The battery and temperature monitor allows an application to continuously monitor on-chip temperature and supply voltage and respond to changes in environmental conditions as needed. The module contains window comparators to interrupt the system CPU when temperature or supply voltage go outside defined windows. These events can also be used to wake up the device from Standby mode through the Always-On (AON) event fabric.

8.10 µDMA

The device includes a direct memory access (μ DMA) controller. The μ DMA controller provides a way to offload data-transfer tasks from the system CPU, thus allowing for more efficient use of the processor and the available bus bandwidth. The μ DMA controller can perform a transfer between memory and peripherals. The μ DMA controller has dedicated channels for each supported on-chip module and can be programmed to automatically perform transfers between peripherals and memory when the peripheral is ready to transfer more data.

Some features of the µDMA controller include the following (this is not an exhaustive list):

- · Highly flexible and configurable channel operation of up to 32 channels
- Transfer modes: memory-to-memory, memory-to-peripheral, peripheral-to-memory, and peripheral-to-peripheral
- Data sizes of 8, 16, and 32 bits
- Ping-pong mode for continuous streaming of data

8.11 Debug

The debug subsystem implements two IEEE standards for debug and test purposes:

IEEE 1149.7 Class 4: Reduced-pin and Enhanced-functionality Test Access port and Boundary-scan Architecture. This is known by the acronym cJTAG (compact JTAG) and this device uses only two pins to communicate to the target: TMS (JTAG_TMSC) and TCK (JTAG_TCKC). This is the default mode of operation

IEEE standard 1149.1: Test Access Port and Boundary Scan Architecture Test Access Port (TAP). This standard is known by the acronym JTAG and this device uses four pins to communicate to the target: TMS (JTAG_TMSC), TCK (JTAG_TCKC), TDI (JTAG_TDI) and TDO (JTAG_TDO).

The debug subsystem also implements a user-configurable firewall to control unauthorized access to debug/test ports.

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English Data Sheet: SWRS195

Also featured is **EnergyTrace/EnergyTrace++**. This technology implements an improved method for measuring MCU current consumption, which features a very high dynamic range (from sub-µA to hundreds of mA), high sample rate (up to 256 kSamples/s) and the ability to track the CPU and peripheral power states.

Two modes of operation can be configured. **EnergyTrace** measures the overall MCU current consumption and allows maximum accuracy and speed to track ultra low-power states as well as the fast power transitions during radio transmission and reception. **EnergyTrace++** tracks the various power states of both the CPU and its Peripherals as well as the system clocks, allowing a close monitoring of the overall device activity.

8.12 Power Management

To minimize power consumption, the CC2652P supports a number of power modes and power management features (see 表 8-1).

MODE	SOFTWARE CONFIGURABLE POWER MODES						
MODE	ACTIVE	IDLE	STANDBY	SHUTDOWN	HELD		
CPU	Active	Off	Off	Off	Off		
Flash	On	Available	Off	Off	Off		
SRAM	On	On	Retention	Off	Off		
Supply System	On	On	Duty Cycled	Off	Off		
Register and CPU retention	Full	Full	Partial	No	No		
SRAM retention	Full	Full	Full	No	No		
48MHz high-speed clock (SCLK_HF)	XOSC_HF or RCOSC_HF	XOSC_HF or RCOSC_HF	Off	Off	Off		
2MHz medium-speed clock (SCLK_MF)	RCOSC_MF	RCOSC_MF	Available	Off	Off		
32kHz low-speed clock (SCLK_LF)	eed clock XOSC_LF or RCOSC_LF		XOSC_LF or RCOSC_LF	Off	Off		
Peripherals	Available	Available	Off	Off	Off		
Sensor Controller	Available	Available	Available	Off	Off		
Wake-up on RTC	Available	Available	Available	Off	Off		
Wake-up on pin edge	Available	Available	Available	Available	Off		
Wake-up on reset pin	on reset pin On		On	On	On		
Brownout detector (BOD)	On	On	Duty Cycled	Off	Off		
Power-on reset (POR)	On	On	On	Off	Off		
Watchdog timer (WDT)	Available	Available	Paused	Off	Off		

表 8-1. Power Modes

In **Active** mode, the application system CPU is actively executing code. Active mode provides normal operation of the processor and all of the peripherals that are currently enabled. The system clock can be any available clock source (see 表 8-1).

In **Idle** mode, all active peripherals can be clocked, but the Application CPU core and memory are not clocked and no code is executed. Any interrupt event brings the processor back into active mode.

In **Standby** mode, only the always-on (AON) domain is active. An external wake-up event, RTC event, or Sensor Controller event is required to bring the device back to active mode. MCU peripherals with retention do not need to be reconfigured when waking up again, and the CPU continues execution from where it went into standby mode. All GPIOs are latched in standby mode.

In **Shutdown** mode, the device is entirely turned off (including the AON domain and Sensor Controller), and the I/Os are latched with the value they had before entering shutdown mode. A change of state on any I/O pin

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defined as a wake from shutdown pin wakes up the device and functions as a reset trigger. The CPU can differentiate between reset in this way and reset-by-reset pin or power-on reset by reading the reset status register. The only state retained in this mode is the latched I/O state and the flash memory contents.

The Sensor Controller is an autonomous processor that can control the peripherals in the Sensor Controller independently of the system CPU. This means that the system CPU does not have to wake up, for example to perform an ADC sampling or poll a digital sensor over SPI, thus saving both current and wake-up time that would otherwise be wasted. The Sensor Controller Studio tool enables the user to program the Sensor Controller, control its peripherals, and wake up the system CPU as needed. All Sensor Controller peripherals can also be controlled by the system CPU.

注

The power, RF and clock management for the CC2652P device require specific configuration and handling by software for optimized performance. This configuration and handling is implemented in the TI-provided drivers that are part of the CC2652P software development kit (SDK). Therefore, TI highly recommends using this software framework for all application development on the device. The complete SDK with TI-RTOS (optional), device drivers, and examples are offered free of charge in source code.

8.13 Clock Systems

The CC2652P device has several internal system clocks.

The 48MHz SCLK_HF is used as the main system (MCU and peripherals) clock. This can be driven by the internal 48MHz RC Oscillator (RCOSC_HF) or an external 48MHz crystal (XOSC_HF). Radio operation requires an external 48MHz crystal.

SCLK_MF is an internal 2MHz clock that is used by the Sensor Controller in low-power mode and also for internal power management circuitry. The SCLK_MF clock is always driven by the internal 2MHz RC Oscillator (RCOSC MF).

SCLK_LF is the 32.768kHz internal low-frequency system clock. It can be used by the Sensor Controller for ultra-low-power operation and is also used for the RTC and to synchronize the radio timer before or after Standby power mode. SCLK_LF can be driven by the internal 32.8kHz RC Oscillator (RCOSC_LF), a 32.768kHz watch-type crystal, or a clock input on any digital IO.

When using a crystal or the internal RC oscillator, the device can output the 32kHz SCLK_LF signal to other devices, thereby reducing the overall system cost.

8.14 Network Processor

Depending on the product configuration, the CC2652P device can function as a wireless network processor (WNP - a device running the wireless protocol stack with the application running on a separate host MCU), or as a system-on-chip (SoC) with the application and protocol stack running on the system CPU inside the device.

In the first case, the external host MCU communicates with the device using SPI or UART. In the second case, the application must be written according to the application framework supplied with the wireless protocol stack.

Product Folder Links: CC2652P

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9 Application, Implementation, and Layout

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For general design guidelines and hardware configuration guidelines, refer to the CC13xx/CC26xx Hardware Configuration and PCB Design Considerations Application Report.

For optimum RF performance, especially when using the high-power PA, it is important to accurately follow the reference design with respect to component values and layout. Failure to do so may lead to reduced RF performance due to balun mismatch. The amplitude- and phase balance through the balun must be <1 dB and <6 degrees, respectively.

PCB stack-up is also critical for proper operation. The CC1352P EVMs and characterization boards are using a finished thickness between the top layer (RF signals) and layer 2 (ground plane) of 175 µm. It is very important to use the same substrate thickness, or slightly thicker, in an end product implementing the CC2652P device.

9.1 Reference Designs

The following reference designs should be followed closely when implementing designs using the CC2652P device.

Special attention must be paid to RF component placement, decoupling capacitors, and DCDC regulator components, as well as ground connections for all of these.

All the CC1352P device reference designs are also applicable to the CC2652P device by simply disregarding the Sub-1GHz RF circuitry. For the CC2652P device, pins 3 and 4 must be left unconnected.

The high-power PA requires a specific RF matching for optimum current efficiency at 10dBm output power (2.4GHz). Refer to the application note Optimizing the SimpleLink CC1352P for Coin Cell Operation at 10dBm Output Power for details.

Integrated matched filter-balun devices can be used both at Sub-1GHz frequencies and at 2.4GHz for the low-power RF outputs. Refer to the "Integrated Passive Component" section in CC13xx/CC26xx Hardware Configuration and PCB Design Considerations for further information.

CC1352PEM-XD7793-XD24-PA24 Design Files

The CC1352PEM-XD7793-XD24-PA24 reference design provides schematic, layout, and production files for the characterization board used for deriving the performance number found in this document. This board includes tuning for 2.4GHz on the high-power PA output.

For the CC2652P device, the Sub-1GHz RF circuitry can be disregarded.

LAUNCHXL-CC1352P-2 Design Files Detailed schematics and layouts for the multiband CC1352P LaunchPad evaluation board featuring 2.4GHz RF matching on the 20dBm PA output and up to 14dBm TX power at 868/915MHz.

For CC2652P, the Sub-1GHz RF circuitry can be disregarded.

Product Folder Links: CC2652P

Sub-1GHz and 2.4GHz Antenna Kit for LaunchPad ™ Development Kit and SensorTag The antenna kit allows real-life testing to identify the optimal antenna for your application. The antenna kit includes 16 antennas for frequencies from 169MHz to 2.4GHz, including:

- PCB antennas
- · Helical antennas
- · Chip antennas
- Dual-band antennas for 868MHz and 915MHz combined with 2.4GHz

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The antenna kit includes a JSC cable to connect to the Wireless MCU LaunchPad development kits and SensorTags.

10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed as follows.

10.1 Tools and Software

The CC2652P device is supported by a variety of software and hardware development tools.

Development Kit

CC1352P-2 LaunchPad™ Development Kit

The CC1352P-2 LaunchPad ™ Development Kit enables the development of high-performance wireless applications in the 863MHz – 930MHz and 2.4GHz frequency bands that benefit from low-power operation. The kit features the CC1352P multiband and multiprotocol SimpleLink Wireless MCU with an integrated High-Power Amplifier. The kit works with the LaunchPad ecosystem, easily enabling additional functionality like sensors, displays, and more. The built-in EnergyTrace ™ software is an energy-based code analysis tool that measures and displays the application's energy profile and helps to optimize it for ultra-low power consumption.

The RF configuration of the LaunchPad enables up to +14dBm output power for 863MHz – 930MHz and +20dBm output power for 2.4GHz.

TMDSEMU110-U Debug Probe

The TMDSEMU110-U Debug Probe enables the development of high-performance wireless applications in the entire family of SimpleLink LaunchPad™ development boards. Featuring a convenient enclosure, which grants the proper mechanical robustness for field and production environments, it supports not only multiple standards such as JTAG/cJTAG/SWD but also a UART backchannel and four GPIOs for maximum debugging flexibility. In addition, the expansion connector allows using the TMDSEMU110-ETH add-on (sold separately), which adds the full-featured XDS110 EnergyTrace™ technology with variable supply voltage from 1.8V to 3.6V and up to 800mA of supply current. The XDS110 EnergyTrace™ technology is a new method for measuring the current consumption that captures the complete operational profile of the wireless MCU.

Software

SimpleLink™ LOWPOWER F2 SDK

The SimpleLink LOWPOWER F2 Software Development Kit (SDK) provides a complete package for the development of wireless applications on the CC13XX / CC26XX family of devices. The SDK includes a comprehensive software package for the CC2652P device, including the following protocol stacks:

- Bluetooth Low Energy 4 and 5.2
- Thread (based on OpenThread)
- · Zigbee 3.0
- TI 15.4-Stack—an IEEE 802.15.4-based star networking solution for Sub-1GHz and 2.4GHz
- EasyLink—a large set of building blocks for building proprietary RF software stacks
- Multiprotocol support—concurrent operation between stacks using the Dynamic Multiprotocol Manager (DMM)

The SimpleLink LOWPOWER F2 SDK is part of TI's SimpleLink MCU platform, offering a single development environment that delivers flexible hardware, software and tool options for customers developing wired and wireless applications. For more information about the SimpleLink MCU Platform, visit https://www.ti.com/simplelink.

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Development Tools

Code Composer Studio™ Integrated Development Environment (IDE)

Code Composer Studio is an integrated development environment (IDE) that supports TI's Microcontroller and Embedded Processors portfolio. Code Composer Studio comprises a suite of tools used to develop and debug embedded applications. It includes an optimizing C/C++ compiler, source code editor, project build environment, debugger, profiler, and many other features. The intuitive IDE provides a single user interface taking you through each step of the application development flow. Familiar tools and interfaces allow users to get started faster than ever before. Code Composer Studio combines the advantages of the Eclipse® software framework with advanced embedded debug capabilities from TI resulting in a compelling feature-rich development environment for embedded developers.

CCS has support for all SimpleLink Wireless MCUs and includes support for EnergyTrace™ software (application energy usage profiling). A real-time object viewer plugin is available for TI-RTOS, part of the SimpleLink SDK.

Code Composer Studio is provided free of charge when used in conjunction with the XDS debuggers included on a LaunchPad Development Kit.

Code Composer Studio™ Cloud IDE

Code Composer Studio (CCS) Cloud is a web-based IDE that allows you to create, edit and build CCS and Energia[™] projects. After you have successfully built your project, you can download and run on your connected LaunchPad. Basic debugging, including features like setting breakpoints and viewing variable values is now supported with CCS Cloud.

IAR Embedded Workbench® for Arm®

IAR Embedded Workbench[®] is a set of development tools for building and debugging embedded system applications using assembler, C and C++. It provides a completely integrated development environment that includes a project manager, editor, and build tools. IAR has support for all SimpleLink Wireless MCUs. It offers broad debugger support, including XDS110, IAR I-jet[™], and Segger J-Link[™]. A real-time object viewer plugin is available for TI-RTOS, part of the SimpleLink SDK. IAR is also supported out-of-the-box on most software examples provided as part of the SimpleLink SDK.

A 30-day evaluation or a 32kB size-limited version is available through iar.com.

SmartRF™ Studio

SmartRF™ Studio is a Windows® application that can be used to evaluate and configure SimpleLink Wireless MCUs from Texas Instruments. The application will help designers of RF systems to easily evaluate the radio at an early stage in the design process. It is especially useful for the generation of configuration register values and for practical testing and debugging of the RF system. SmartRF Studio can be used either as a standalone application or together with applicable evaluation boards or debug probes for the RF device. Features of the SmartRF Studio include:

- Link tests—send and receive packets between nodes
- Antenna and radiation tests—set the radio in continuous wave TX and RX states
- · Export radio configuration code for use with the TI SimpleLink SDK RF driver
- Custom GPIO configuration for signaling and control of external switches

Product Folder Links: CC2652P

Sensor Controller Studio

Sensor Controller Studio is used to write, test and debug code for the Sensor Controller peripheral. The tool generates a Sensor Controller Interface driver, which is a set of C source files that are compiled into the System CPU application. These source files also contain the Sensor Controller binary image and allow the System CPU application to control and exchange data with the Sensor Controller. Features of the Sensor Controller Studio include:

Ready-to-use examples for several common use cases

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- Full toolchain with built-in compiler and assembler for programming in a C-like programming language
- Provides rapid development by using the integrated sensor controller task testing and debugging functionality, including visualization of sensor data and verification of algorithms

CCS UniFlash

CCS UniFlash is a standalone tool used to program on-chip flash memory on TI MCUs. UniFlash has a GUI, command line, and scripting interface. CCS UniFlash is available free of charge.

10.1.1 SimpleLink™ Microcontroller Platform

The SimpleLink microcontroller platform sets a new standard for developers with the broadest portfolio of wired and wireless Arm® MCUs (System-on-Chip) in a single software development environment. Delivering flexible hardware, software and tool options for your IoT applications. Invest once in the SimpleLink software development kit and use throughout your entire portfolio. Learn more on ti.com/simplelink.

10.2 Documentation Support

To receive notification of documentation updates on data sheets, errata, application notes and similar, navigate to the device product folder on ti.com/product/CC2652P. In the upper right corner, click on Alert me to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

The current documentation that describes the MCU, related peripherals, and other technical collateral is listed as follows.

TI Resource Explorer

TI Resource Explorer Software examples, libraries, executables, and documentation are available for your device and development board.

Errata

CC2652P Silicon Errata

The silicon errata describes the known exceptions to the functional specifications for each silicon revision of the device and description on how to recognize a device revision.

Application Reports

All application reports for the CC2652P device are found on the device product folder at: ti.com/product/ CC2652P/technicaldocuments.

Technical Reference Manual (TRM)

CC13x2, CC26x2 SimpleLink™ Wireless **MCU TRM**

The TRM provides a detailed description of all modules and peripherals available in the device family.

10.3 サポート・リソース

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10.6 用語集

テキサス・インスツルメンツ用語集 この用語集には、用語や略語の一覧および定義が記載されています。



11 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Cha	anges from Revision B (February 2021) to Revision C (April 2024)	Page	
	セクション 1 のシャットダウン電流の値を変更		
	Changed "terminal" to "pin"		
	Jpdated Operating junction temperature range		
	Jpdated Radio TX Current		
	Jpdated MCU, Reset to Active Timing		
	Jpdated MCU, Shutdown to Active Timing		
• (Jpdated DAC Offset error	23	
• (Jpdated DAC Max code output voltage variation	<mark>23</mark>	
• /	Added LAUNCHXL-CC1352P-2 Design Files to セクション 9.1	47	
	bruary 2021)) ヾキュメント全体を通して Bluetooth 5.2 に更新	Page 1	
	、マュメント全体を通じ (Bidetooth 5.2 に受利 セクション 1 の「特長」で「無線」セクションのリストに 3 線、2 線、1 線 PTA 共存メカニズムを追加		
	わか、ハノ4の「烘目」で「ロノみレフプロレコルルフトの頂目から Wi CLIN も判除		
	セクション 1 の「特長」で「ワイヤレス プロトコル」リストの項目から Wi-SUN を削除	1	
	Changed the test condition to "Zero cycles" for the Flash sector erase time parameter in セクション	1 7.7,	
• (Changed the test condition to "Zero cycles" for the Flash sector erase time parameter in セクション `Nonvolatile (Flash) Memory Characteristics	1 7.7, 9	
	Changed the test condition to "Zero cycles" for the Flash sector erase time parameter in セクション (Nonvolatile (Flash) Memory Characteristics	1 7.7, 9 'Flash)	
٨	Changed the test condition to "Zero cycles" for the Flash sector erase time parameter in セクション (Nonvolatile (Flash) Memory Characteristics	1 7.7, 9 <i>Flash</i>) 9	
. (Changed the test condition to "Zero cycles" for the Flash sector erase time parameter in セクション Nonvolatile (Flash) Memory Characteristics	1 7.7, 9 (Flash) 9	
• (Changed the test condition to "Zero cycles" for the Flash sector erase time parameter in セクション Nonvolatile (Flash) Memory Characteristics	1 7.7,9 Flash)9 Sensor 26	
· ()	Changed the test condition to "Zero cycles" for the Flash sector erase time parameter in セクション Nonvolatile (Flash) Memory Characteristics		

Reference Designs47

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12 Mechanical, Packaging, and Orderable Information

12.1 Packaging Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
	. ,	.,			. ,	(4)	(5)		, ,
CC2652P1FRGZR	Active	Production	VQFN (RGZ) 48	2500 LARGE T&R	Yes	NIPDAU NIPDAUAG	Level-3-260C-168 HR	-40 to 85	CC2652 P1F
CC2652P1FRGZR.A	Active	Production	VQFN (RGZ) 48	2500 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 85	CC2652 P1F
CC2652P1FRGZR.B	Active	Production	VQFN (RGZ) 48	2500 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 85	CC2652 P1F

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

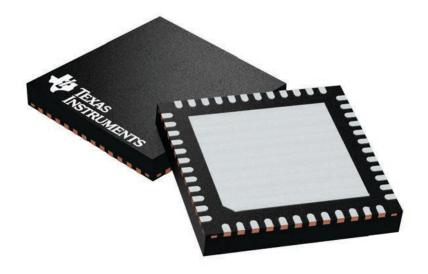
⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

7 x 7, 0.5 mm pitch

PLASTIC QUADFLAT PACK- NO LEAD

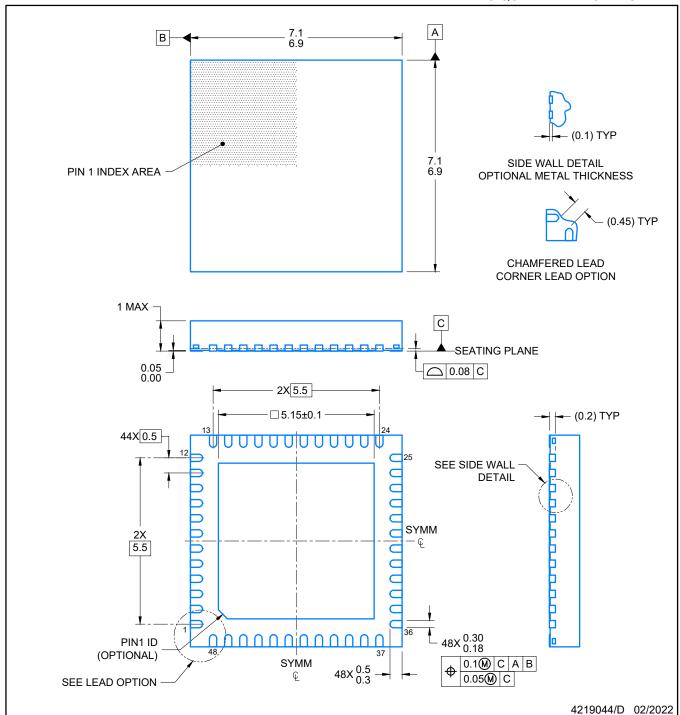


Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4224671/A



PLASTIC QUADFLAT PACK- NO LEAD

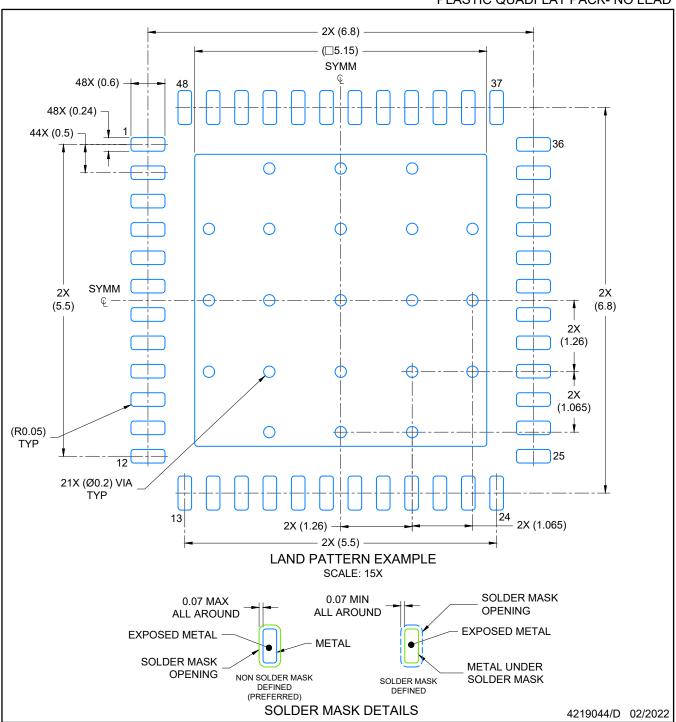


NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



PLASTIC QUADFLAT PACK- NO LEAD

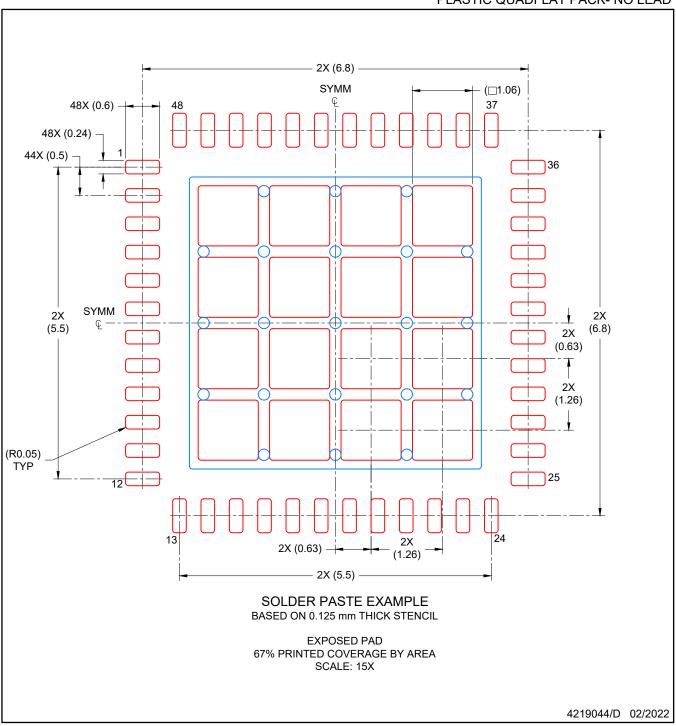


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUADFLAT PACK- NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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